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# **Department of Electronics and Communication Engineering**

## **Master of Technology**

**VLSI Design and Systems** 

Curriculum



### **University Vision**

We visualize Graphic Era (Deemed to be University) as an internationally recognized, enquiry driven, ethically engaged diverse community, whose members work collaboratively for positive transformation in the world, through leadership in teaching, research and social action.

### **University Mission**

The mission of the university is to promote learning in true spirit and offering knowledge and skills in order to succeed as professionals. The university aims to distinguish itself as a diverse, socially responsible learning community with a high-quality scholarship and academic rigor.

### **Department Vision**

The Department visualizes itself to become leading centre of learning in the field of Electronics & Communication Engineering with academic excellence in research to produce self-motivated, creative, and socially responsible engineers and specialists, ready to take up challenges of industrial development with ethics and societal commitment.

## **Department Mission**

M1: To provide high quality contemporary education in the field of Electronics & Communication Engineering and professional ethics to its learners.

M2: To provide creative learning environment for the students to equip them with strong foundation for continuing higher education.

M3: To pursue research and develop insight knowledge of current and emerging technologies in Electronics & Communication Engineering to serve the needs of the society, industry, and scientific community.

M4: To prepare students to have creative and innovative thinking to develop them into socially responsible professionals



## **Program Educational Objectives (PEOs):**

PEO1	Implementation of core-engineering knowledge to solve practical problems in the areas of VLSI design and Systems, and to produce innovative systems in these domains.
PEO2	Motivating entrepreneurship in VLSI domains by integration of sustainability with efficiently designed systems.
PEO3	Sharpening the educational, and research-oriented skills of the students for their easy merger into a future career in research or academia.
PEO4	Developing the design engineers with excellent ability to communicate, along with a morally responsible behavior.



## **Program Outcomes (POs):**

PO1	Apply the knowledge of science, mathematics, and engineering principles for developing problem solving attitude.
PO2	Identify, formulate, and solve engineering problems in the broad areas like System Design using VLSI.
PO3	Use different modern engineering software tools in the domain of VLSI and Systems Design.
PO4	Design and conduct experiments, analyze and interpret data, imbibe programming skills for development of simulation experiments.
PO5	Function as a member of a multidisciplinary team with sense of ethics, integrity, and social responsibility.
PO6	Realize the need for self-education and ability for independent and life-long learning.

## **Program Specific outcomes (PSOs):**

PSO1	Attain competency in areas of IC designing, testing, and developing prototype of various VLSI circuits.						
PSO2	Integrating various VLSI sub-systems to design industrial circuits.						
PSO3	Students gain skills in developing various complicated circuits and excel in industrial sector.						



### **Program Course Structure (All Semesters)**

#### M. Tech (VLSI Design and Systems)

(Batch 2022 onwards)

#### **Semester I**

	Course Module					Teaching Weightage:					e:
Theory Subjects				Periods			Evaluation				
SI. No.	Code	Course title	Component	Credits	L	Т	P	CWA	MSE	ESE	Total
1	VDM 101	Semiconductor Materials and Devices	PC	3	3	0	0	25	25	50	100
2	VDM 102	CMOS Analog Circuit Design	PC	3	3	0	0	25	25	50	100
3	VDM 103	Advanced Digital Integrated Circuit	PC	3	3	0	0	25	25	50	100
4	VDM 104	VLSI Technology	PC	3	3	0	0	25	25	50	100
5	VDM -	Program Elective-I	PE	3	3	0	0	25	25	50	100
		Laboratory and Others									
6	VDM 151	CMOS Analog Circuit Design Lab	PC	2	0	0	4	25	25	50	100
7	VDM 152	Digital VLSI Circuit Design Lab	PC	2	0	0	4	25	25	50	100
8	GP101	General Proficiency	GP	1	0	0	0	0	0	100	100
		TOTAL		20	15	00	08				800



## M. Tech (VLSI Design and Systems) (Batch 2022 onwards) Semester II

	Course Module					eachi	ng		Wei	ghtag	e <b>:</b>
Theory Subjects					eriod				luatio		
SI. No.	Code	Course title	Component	Credits	L	Т	P	CWA	MSE	ESE	Total
1	VDM 201	Advanced ASIC and FPGA Design	PC	3	3	0	0	25	25	50	100
2	VDM 202 Digital System Design using Verilog HDL		PC	3	3	0	0	25	25	50	100
3	VDM 203	Advanced VLSI Circuit Testing	PC	3	3	0	0	25	25	50	100
4	VDM 204	Low Power VLSI Design	PC	3	3	0	0	25	25	50	100
5	5 VDM Program Elective-II		PE	3	3	0	0	25	25	50	100
		Laboratory and Oth	ers								
6	VDM 251	Verilog HDL Lab	PC	2	0	0	4	25	25	50	100
7	VDM 252	VLSI Physical Design Lab	PC	2	0	0	4	25	25	50	100
8	VDM 253	Mini Project with Seminar	PROJ	2	0	0	4	25	0	75	100
9	GP 201	General Proficiency	GP	1	0	0	0	0	0	100	100
		TOTAL		22	15	00	12				900



## M. Tech (VLSI Design and Systems) (Batch 2022 onwards) Semester III

	Course Module					eachi	ng		Wei	ghtage	e:
Theory Subjects			Periods				Evaluation				
SI. No.	Code	Course title	Component	Credits	L	Т	P	CWA	MSE	ESE	Total
1	VDM	Program Elective-III	PE	3	3	0	0	25	25	50	100
2	VOM	Open Elective	OE	3	3	0	0	25	25	50	100
		Laboratory and Oth	ers								
3	VDM 351	Modelling and Simulation Lab	PC	2	0	0	4	25	25	50	100
4	VDM 301	Dissertation Phase-I*	PROJ	10	0	0	20	25	50	125	200
5	GP 301	General Proficiency	GP	1	0	0	0	0	0	100	100
		TOTAL		19	06	00	24				600

<sup>\*</sup>Students going for Industrial Project/Thesis will complete these courses through MOOCs.



## M. Tech (VLSI Design and Systems) (Batch 2022 onwards) Semester IV

	Course Module				Teaching Periods			Weightage: Evaluation			
Sl. No.	Code	Course title	Component	Credits	L	Т	P	CWA	MSE	ESE	Total
1	VDM 401	Dissertation Phase-II	PROJ	16	0	0	32	50	100	250	400
2	GP 401	General Proficiency	GP	1	0	0	0	0	0	100	100
		TOTAL		17	00	00	32				500



## M. Tech (VLSI Design and Systems) (Batch 2022 onwards) Program Electives and Open Electives

	<b>Program Elective Courses</b>						
Course Code	l Course Name						
Program Elective I							
VDM 191	Advanced Nanotechnology						
VDM 192	Optimization Techniques in VLSI Design						
VDM 193	Theory and Application of Embedded Systems	Fina4					
VDM 194	Digital Signal Processing for VLSI	First					
VDM 195	Robust Control System						
VDM 196	Control of Advanced Electric Machine						
	Program Elective II						
VDM 291	Micro-Sensors and MEMS						
VDM 292	RF Microelectronics Devices						
VDM 293	VLSI Circuits for Biomedical Application						
VDM 294	Microwave & MM-wave Integrated Circuits and Applications	Second					
VDM 295	Renewable Energy Resources and Energy Management						
VDM 296	Multivariable Control System						
	Program Elective III						
VDM 391	Organic Electronics Devices and Circuits						
VDM 392	Memory Design and Testing						
VDM 393	System on Chip Design and Testing	Third					
VDM 394	VLSI Physical Design Automation						
VDM 395	Power Quality Assessment						
VDM 396	Optimal & Adaptive Control						



	Open Elective Courses						
Course Code	Course Name	Semester					
VOM 301	Cloud Computing						
VOM 302	Internet of Things	Third					
VOM 303	Artificial Intelligence and expert systems	1 mira					
VOM 304	Soft Computing						

### **Abbreviations:**

L	Lecture
T	Tutorial
P	Practical
CWA	Class Work Assessment
MSE	Mid Semester Exam
ESE	End Semester Exam
PC	Program Core
PE	Program Elective
OE	Open Elective
PROJ	Project
GP	General Proficiency*

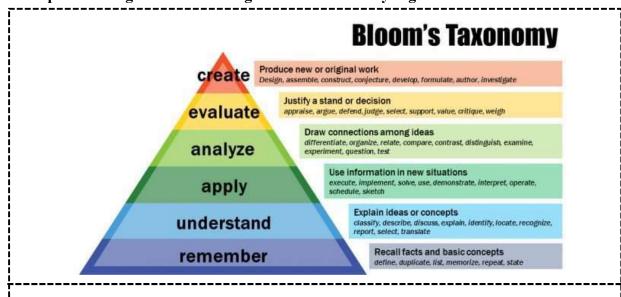
<sup>\*</sup>Institution Initiative



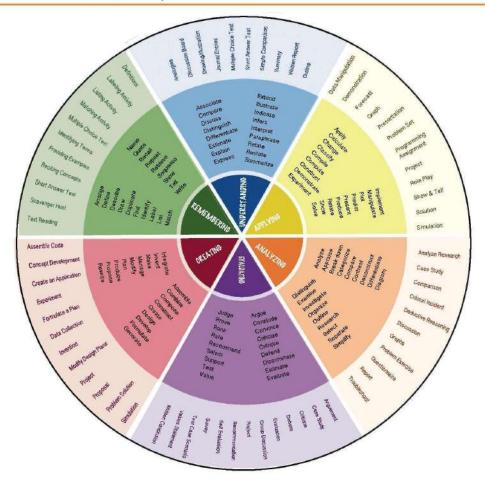
## **Bloom's Taxonomy for Curriculum Design and Assessment**

#### **Preamble**

The design of curriculum and assessment is based on Bloom's Taxonomy. A comprehensive guideline for using Bloom's Taxonomy is given below for reference.









	Depo	artment of Electron	ics and Communication E	ngineerin	ıg					
	•		ter of Technology	G	J					
		VLSI I	Design and Systems							
Semester	First	Subject Title	Semiconductor Materia Devices	ıls and	Code	VDM 101				
Course Co	omponents	Credits	Contact Hours	L	T	P				
Program	Core (PC)	03	Contact Hours	3	0	0				
	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE				
Duratio	on (Hrs)	03	Weightage. Livatuation	25	25	50				
	Pre-requisit	e: Basic Electronics	Engineering, Electronic D	evices an	d Circuits					
		Ca	ourse Outcomes							
Upon com	pletion of th	nis course, the stud	ents will be able to							
CO 1	Create bas	ic understanding of	semiconductor device phys	sics.						
CO 2	Evaluate t	wo terminal MOS st	ructure in terms of its elect	rical para	meters.					
CO 3	Analyse th	e three terminal MC	S structure in terms of elec	ctrical pot	ential and	charge.				
CO 4	Apply surf	ace potential and ch	arges in different regions o	f MOSFE	ET operation	on.				
CO 5	Understan	d the short channel	and narrow channel effects	<b>).</b>						
CO 6	<b>Implement</b> application		semiconductor device phy	sics in o	developing	real life				
Unit No.	Content					Hours				
Unit 1:	Semicondu	ctor materials,	-	Basics of Semiconductors: Semiconductor materials, Energy levels, Intrinsic and extrinsic 8						
semiconductor, Equilibrium in absence/presence of electric field.  PN Junction Diode:  Junction diode: PN junction, Tunnel diode, Quasi-fermi levels, Depletion width capacitance and its application in doping profile determination, I-V characteristics of narrow and wide base diodes and their equivalent circuits, Breakdown mechanisms, Small signal ac impedance.										
Unit 2:	Junction di width capa characteris	iode: PN junction, 'citance and its applitics of narrow and w	Tunnel diode, Quasi-fermi lication in doping profile of vide base diodes and their e	levels, I	tion, I-V	8				
Unit 2: Unit 3:	Junction di width capa characterist Breakdown Two Term Flat band v voltage on	iode: PN junction, 'citance and its applitics of narrow and was mechanisms, Smalninal MOS Structuroltage, Potential ball	Tunnel diode, Quasi-fermilication in doping profile of vide base diodes and their ell signal ac impedance.  Te:  lance and charge balance, Electronical description, Depletion, I	levels, I determina equivalent	tion, I-V t circuits,	8				
	Junction di width capa characterist Breakdown Two Term Flat band v voltage on analysis, St Three Ter Contacting Pinch-off v	iode: PN junction, icitance and its applitics of narrow and we mechanisms, Smallinal MOS Structure oltage, Potential bal surface condition, amall signal capacitate minal MOS Structure the inversion layer, roltage.	Tunnel diode, Quasi-fermi lication in doping profile of vide base diodes and their ell signal ac impedance.  Te:  Iance and charge balance, Faccumulation, Depletion, Ince.  Ure:  Body effect, Different reg	levels, I determina equivalent Effect of g	tion, I-V t circuits, gate body General					
Unit 3:	Junction di width capa characterist Breakdowr Two Term Flat band v voltage on analysis, St Three Ter Contacting Pinch-off v Four Term Transistors region modin terms of	iode: PN junction, icitance and its applitics of narrow and we mechanisms, Smallinal MOS Structuroltage, Potential bal surface condition, amall signal capacitate minal MOS Structuroltage.  Ininal MOS Structuroltage.	Tunnel diode, Quasi-fermi lication in doping profile of vide base diodes and their ell signal ac impedance.  Te:  I ance and charge balance, Ell Accumulation, Depletion, Ince.  The complete all-region modern quasi fermi potential, Resemperature effects, Breakdo	levels, I determina equivalent Effect of gions of o	gate body General operation,	10				

	Textbooks						
1.	Tsividis, Yannis, and Colin McAndrew, "Operation and Modelling of the MOS Transistor",						
	Oxford: Oxford University Press, Vol. 2, 3 <sup>rd</sup> Edition, 2003.						



S. Kang and Y. Leblebici, "CMOS Digital Integrated Circuits, Analysis and Design", 3rd Edition, Tata McGraw-Hill, 2003.
 Reference Books
 Robert L. Boylestad and Louis Nashelsky, "Electronic Devices and Circuit Theory", 9th Edition, Prentice Hall of India (PHI), 2006.
 Ben g. Streetman and Sanjay Kumar Banerjee, "Solid State Electronic Devices", 6th Edition, Prentice Hall of India (PHI), 2013.

5. Takayasu Sakurai, Akira Matsuwawa and Takakuni Douseki, "Fully-Depleted SOI CMOS Circuits and Technology for Ultralow power applications", 1st Edition, Springer, 2006.

Mode of Evaluation Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



1	<b>n</b> .	auton and of FI4:	ion and Communication E				
Department of Electronics and Communication Engineering  Master of Technology							
			Design and Systems				
Semester	Semester         First         Subject Title         CMOS Analog Circuit Design         Code						
Course C	omponents	Credits	Control House	L	T	P	
Program	Core (PC)	03	Contact Hours	3	0	0	
Exam	Examination Theory Weightage Evaluation CWA MSE						
Duratio	on (Hrs)	03	Weightage: Evaluation	25	25	50	
		<b>Pre-requisite:</b> Ele	ectronics Devices and Circ	uits			
		Co	urse Outcomes				
Upon com	pletion of th	nis course, the stude	ents will be able to				
CO 1	-		g IC design in CMOS techr				
CO 2			vith different configuration				
CO 3			ge and differential MOS ar	nplifiers.			
CO 4		e current mirror circ					
CO 5			back amplifiers and phase l	ocked lo	op.		
CO 6	Design and	l <b>develop</b> various CN	MOS analog circuits.				
	•						
Unit No.	Content					Hours	
Unit 1:	Models for Integrated Circuit Active Devices:  The depletion region of a PN junction, Depletion region capacitance and junction breakdown, Basics of MOS transistor, Derivation of current-voltage relationship, Analysis of MOS as an amplifier, Small signal models of MOS transistor, MOS transistor frequency response.				8		
Unit 2:	Single Stage Amplifier: Common source stage with resistive load, CS stage with diode connected load, CS stage with current source load, CS stage with triode load, CS stage with source generation, Source follower and common gate configuration.						
	Multistage Amplifier and Operational Amplifier: Cascode current source, Cascode amplifier, Differential pair, Small and large signal analysis of differential amplifier, Differential amplifier with MOS loads, OPAMP design: General consideration, One stage OpAmp					9	
Unit 3:	Cascode cu signal anal	e Amplifier and Operrent source, Cascod lysis of differential	erational Amplifier: le amplifier, Differential pa amplifier, Differential am	e configur ir, Small plifier w	ration. and large		
Unit 3: Unit 4:	Cascode cu signal anal loads, OPA Current M Simple cu Common s	e Amplifier and Operrent source, Cascod lysis of differential AMP design: General lirrors, Active Load rrent mirror, Casco source amplifier with	erational Amplifier: le amplifier, Differential pa amplifier, Differential am l consideration, One stage (	ir, Small plifier w DpAmp  n curren oltage an	and large ith MOS t mirror, d current		
	Cascode cusignal anal loads, OPA Current M Simple cus Common s references: Feedback General	e Amplifier and Operrent source, Cascod lysis of differential AMP design: General lirrors, Active Load rrent mirror, Casco source amplifier with Widlar and peaking and Non-Linear Arconsideration, Properrent of the Property of the Amplifier with the Property of the Amplifier and Property of the Property of the Amplifier and Property of the Amplifier and Property of the Amplifier and Open State of the O	erational Amplifier: le amplifier, Differential pa amplifier, Differential am consideration, One stage of ds and References: le current mirror, Wilso h complementary load, Vo current sources, supply ins	e configuration ir, Small plifier w DpAmp n curren bltage an sensitive	and large ith MOS  t mirror, d current biasing.	9	

	Textbooks
1.	B. Razavi, "Design of analog CMOS Integrated Circuits", McGraw-Hill, 1st Edition, 2002.
2.	Mohammed Ismail and Terri Faiz, " <i>Analog VLSI Signal and Information Process</i> ", McGraw-Hill, 1 <sup>st</sup> Edition, 1994.



#### Reference Books

- **3.** Paul R. Gray and R. G. Meyer, "*Analysis and Design of Analog Integrated Circuits*" John Wiley and Sons", 4<sup>th</sup> Edition, 2001.
- **4.** R. Jacob Baker, H. W. Li, and D.E. Boyce, "*CMOS: Circuit Design, Layout and Simulation*", Prentice-Hall of India, 3<sup>rd</sup> Edition, 2010.

<b>Mode of Evaluation</b>	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



Department of Electronics and Communication Engineering							
	Master of Technology						
	VLSI Design and Systems						
Semester	Semester First Subject Title Advanced Digital Integrated Circuit Code				VDM 103		
Course Co	mponents	Credits	Control House	L	T	P	
Program (	Core (PC)	03	Contact Hours	3	0	0	
Exami	nation	Theory	Wajahtaan Englustion	CWA	MSE	ESE	
Duratio	n (Hrs)	03	- Weightage: Evaluation	25	25	50	
	Pre-req	uisite:Basic Electro	nics Engineering and Digit	al Electro	onics		
		Ca	ourse Outcomes				
Upon com	pletion of th	nis course, the stud	ents will be able to				
CO 1	Describe tl	he basic MOS struct	ure and layout design.				
CO 2	Understan	d the static and dyn	amic characteristics of MO	S inverte	rs.		
CO 3	Apply the	MOS concepts to de	sign combinational and sec	quential N	MOS logic	circuits.	
CO 4	Analyse di	fferent digital MOS	logic circuits.				
CO 5			of CMOS logic circuits.				
CO 6	_	various concepts of sed digital circuits.	digital VLSI circuit design	and appl	y them in	designing	
Unit No.	Content					Hours	
Unit 1:	Introduction and Implementation of strategies for digital ICs: Issues in Digital Integrated Circuit Design, Quality Metrics of a Digital Design, Design rule: Stick diagram and layout. Custom Circuit design, Cell based and Array based design implementations.						
Unit 2:	MOS Inve Static and Logical eff	Dynamic Character	ristics of CMOs inverter, I	Power dis	ssipation,	10	
Unit 3:	Designing combinational and sequential circuits: Static CMOS design, Different styles of logic circuits, Logical effort of complex gates, Static and dynamic properties of complex gates, Dynamic CMOS Logic. Timing metrics of sequential circuits, Dynamic latches and Registers. Pipelining.					10	
Unit 4:	Interconnect and Timing Issues: Circuit characterization and performance estimation - Resistance, Capacitance estimation - Switching characteristics - Delay models – Timing issues in Digital circuits, Power dissipation. Impact of Clock Skew and Jitter.						
Unit 5:	Memory Design: Read-Only Memories, ROM cells, Read-write memories (RAM), dynamic memory design, 6 transistor SRAM cell, Sense amplifiers						
Onu 3:	_		*		dynamic	6	

	Textbooks					
1.	S. Kang and Y. Leblebici, "CMOS Digital Integrated Circuits, Analysis and Design", Tata					
	McGraw-Hill, 3 <sup>rd</sup> Edition, 2003.					



2.	J. M. Rabaey, A. Chandrakasan and B. Nikolic, "Digital Integrated Circuits: A Design
	<i>Perspective</i> ", Prentice-Hall of India, 2 <sup>nd</sup> Edition, 2006.
	Reference Books
3.	John P. Uyemura, "Introduction to VLSI Circuits", Wiley India Pvt. Ltd,1st Edition 2012
4.	Eugene Fabricius, "Introduction to VLSI Design", New Ed Edition, Tata McGraw -
	Hill Education, 1990
5.	N. H. E. Weste et. al., "CMOS VLSI Design", Pearson, 3rd Edition, 2005.
6.	R. Jacob Baker, "CMOS: circuit design, layout, and simulation", John Wiley & Sons, 3 <sup>rd</sup>
	Edition, 2010.

<b>Mode of Evaluation</b>	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



Department of Electronics and Communication Engineering  Master of Technology  VLSI Design and Systems  Samester First Subject Title VISI Technology Code					
VLSI Design and Systems					
Semester First Subject Title VLSI Technology Code					
Course Components Credits Contact Hours L T	P				
Program Core (PC) 03 3 0	0				
Examination Theory Weightage: Evaluation CWA MSE	ESE				
Duration (Hrs) 03 25 25	50				
Pre-requisite: VLSI Technology and Design					
Course Outcomes					
Upon completion of this course, the students will be able to  CO 1 Explain about wafer fabrication techniques and oxidation process.					
<ul> <li>CO 1 Explain about wafer fabrication techniques and oxidation process.</li> <li>CO 2 Analyse photolithography and etching techniques of VLSI design.</li> </ul>					
CO 3 Extend the knowledge of different physical and chemical deposition methods.					
CO 4 Investigate metal deposition techniques and IC fabrication methodologies.					
CO 5 Design and analysis of different packaging methods.					
CO 6 Create a base for the semiconductor device fabrication using VLSI technology.					
ereact weapon for the seminorial active morround asing their recinioregy.					
Unit No.   Content   H	Hours				
<ul> <li>Wafer Preparation and Oxidation:         <ul> <li>Electron grade silicon, Crystal growth, Wafer preparation, Processing considerations, Vapor phase epitaxy and molecular beam epitaxy, Film characteristics, SOI structure, Oxide formation, Kinetics, Oxidation systems, Dry and wet oxidation, Masks properties of SiO<sub>2</sub>, Oxidation defects, Redistribution of dopant at interface, Oxidation of poly silicon.</li> </ul> </li> </ul>	0				
Unit 2: Lithography and Etching: Optical, Electron, X-Ray and Ion Lithography methods, Positive and negative photo resist. Plasma properties, Size, Control, Etch mechanism, Etch techniques and equipment.					
Unit 3:  Deposition and diffusion: Deposition process and methods, Diffusion in solids, Diffusion equation and Diffusion mechanisms, Flick's one-dimensional diffusion equation, Atomic diffusion mechanism, Measurement techniques, Range theory, Implant equipment, Ion implantation, Damage and annealing, Ion implantation systems.					
<ul> <li>Unit 4: Metallization and IC Fabrication:         Metallization and its applications, Process simulation of Ion implementation,         Diffusion, Oxidation, Epitaxy, Lithography, Etching and deposition,         Annealing shallow junction – High energy implantation, Physical vapours deposition patterning. NMOS, CMOS and bipolar IC technologies and IC fabrication.</li> </ul>					
Fin-FET Process Flow and Packaging: Fin-FET manufacturing technology, Bulk Fin-FET fabrication, SOI Fin-FET process flow. Analytical and assembly techniques and packaging of VLSI devices.					



	Textbooks					
1.	S. M. Sze, "VLSI Technology", McGraw Hill, 2 <sup>nd</sup> Edition, 1988.					
2.	W. Wolf, "Modern VLSI Design", Pearson, 3rd Edition, 2002.					
	Reference Books					
3.	S. K. Gandhi, " <i>VLSI Fabrication Principles Silicon and Gallium Arsenide</i> ", Wiley-INDIA, 2 <sup>nd</sup> Edition, 1994.					
4.	Wai Kai Chen, "VLSI Technology", CRC press, 1st Edition, 2003.					
5.	Samar K Saha,, "FinFET Devices for VLSI Circuits and Systems", CRC Press, 1st Edition,					
	2020.					

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.





Department of Electronics and Communication Engineering						
Master of Technology						
	VLSI Design and Systems					
<b>Semester</b> First		Subject Title	CMOS Analog Circuit Desi Lab		Code	VDM 151
Course Co	omponents	Credits	Contact Hours	L	T	P
ŭ	Core (PC)	02	Contact Hours	0	0	4
	ination	Practical	Weightage: Evaluation	CWA	MSE	ESE
Duratio	on (Hrs)	03		25	25	50
	Pre-requisit		es and Circuit, VLSI Tech	nology ar	nd Design	
			urse Outcomes			
		nis course, the stude				
CO 1		d Cadence Virtuoso		11.0	. ~ .	
CO 2			on drain, and operational a			ence tool.
CO 3	i e		CMOS based circuits using			
CO 4	Integrate t	the acquired knowled	lge for developing CMOS	based cir	cuits.	
T M	N C.11	E				
Exp. No.	T .	ne Experiment				
1.		ew cell view and bui ource amplifier using	ld common source amplifig 45 nm technology.	er and cre	eate a syml	bol for the
2.		of common source	amplifier test circuit using.	ng comm	on source	amplifier
3.	Create a la	yout of common sou	rce amplifier using 45 nm	technolog	gy.	
4.	_	ew cell view and burain amplifier using	ild common drain amplific 45 nm technology.	er and cre	ate a symb	ool for the
5.	Simulation		nplifier test circuit using co	mmon dr	ain amplifi	er symbol
6.			in amplifier using 45 nm te	chnology	7.	
7.	Design a n		uild Differential amplifier			ool for the
8.		of Differential ampl	ifier test circuit using Diffe	rential am	nplifier syn	nbol using
9.			amplifier using 45 nm tech	nology.		
10.	Design a r		uild operational amplifier		ite a symb	ol for the
11.	Simulation of operational amplifier test circuit using operational amplifier symbol using					
12.			Amplifier using 45 nm tech	nology.		
Innovativ		•				
13.	T .	simulation of currer	nt mirror circuits using 45	nm techn	ology.	
14.						
Mode of	Evaluation		/ Assignment / Mid Term I			xam
		-	-			



Semester   First   Subject Title   Digital VLSI Circuit Design Lab   Code   VDM   152	Department of Electronics and Communication Engineering							
Semester   First   Subject Title   Digital VLSI Circuit Design Lab   Code   VDM   152								
Course Components   Credits   Contact Hours   L   T   P								
Program Core (PC)	<b>Semester</b> First		Subject Title	Digital VLSI Circuit Design Lab		Code		
Program Core (PC)   02				Contact Hours				
Duration (Hrs)   03   Weightage: Evaluation   25   25   50				Commen 110m/s				
Pre-requisite: Digital Electronics  Course Outcomes  Upon completion of this course, the students will be able to  CO 1 Understand the CMOS based digital integrated circuits.  CO 2 Analyse CMOS based sequential circuits using 180 nm Technology.  CO 3 Evaluate CMOS based sequential circuits using 180 nm Technology.  CO 4 Design and validate various CMOS based digital circuits using Cadence tool.  Exp. No. Name of the Experiment  1. Design and comparison of DC and transient output characteristics of CMOS inverter at different aspect ratio.  2. Draw a layout of CMOS inverter using 45 nm technology and check for LVS and DRC for inverter circuit.  3. Design and implement various gates with CMOS logic along with its layout.  4. Draw a schematic of half adder/full adder using 45 nm technology and analyse its transient characteristics.  5. Draw the layouts of half adder/full adder using 45 nm technology and simulate its transient characteristics.  6. Design a schematic of comparator using 45 nm technology and simulate its transient characteristics.  7. Design and Implementation of 2:1 Multiplexer and 1:2 Demultiplexer.  8. Design the schematic of latches using 45 nm technology and simulate its transient characteristics  9. Design the schematic of flip-flops using 45 nm technology and simulate its transient characteristics  10. Design the schematic of shift register using 45 nm technology and simulate its transient characteristics  11. Design the schematic of up/down counter using 45 nm technology and simulate its transient characteristics  12. Design the schematic of of TRAM using 45 nm technology and simulate its transient characteristics  13. Design the schematic of of TRAM using 45 nm technology and simulate its transient characteristics  14. Design the schematic of of TRAM using 45 nm technology and simulate its transient characteristics  15. Simulate substrate bias (Body) effect in CMOS inverter.				Weightage: Evaluation				
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CO 1 Understand the CMOS based digital integrated circuits. CO 2 Analyse CMOS based combinational circuits using 180 nm Technology. CO 3 Evaluate CMOS based sequential circuits and memory devices. CO 4 Design and validate various CMOS based digital circuits using Cadence tool.  Exp. No. Name of the Experiment  1. Design and comparison of DC and transient output characteristics of CMOS inverter at different aspect ratio.  2. Draw a layout of CMOS inverter using 45 nm technology and check for LVS and DRC for inverter circuit. 3. Design and implement various gates with CMOS logic along with its layout.  4. Draw a schematic of half adder/full adder using 45 nm technology and analyse its transient characteristics.  5. Draw the layouts of half adder/full adder using 45 nm technology and simulate its transient characteristics.  6. Design a schematic of comparator using 45 nm technology and simulate its transient characteristics  7. Design and Implementation of 2:1 Multiplexer and 1:2 Demultiplexer.  8. Design the schematic of latches using 45 nm technology and simulate its transient characteristics  9. Design the schematic of flip-flops using 45 nm technology and simulate its transient characteristics  10. Design the schematic of shift register using 45 nm technology and simulate its transient characteristics  11. Design the schematic of up/down counter using 45 nm technology and simulate its transient characteristics  12. Design the schematic of up/down counter using 45 nm technology and simulate its transient characteristics  13. Design and implementation of Flash Memory with Cadence tool.  14. Design and implementation of Different Analog to Digital converter (ADC) with Cadence tool.  15. Simulate substrate bias (Body) effect in CMOS inverter.	Unon com	nletion of th						
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characteristics  7. Design and Implementation of 2:1 Multiplexer and 1:2 Demultiplexer.  8. Design the schematic of latches using 45 nm technology and simulate its transient characteristics  9. Design the schematic of flip-flops using 45 nm technology and simulate its transient characteristics  10. Design the schematic of shift register using 45 nm technology and simulate its transient characteristics  11. Design the schematic of up/down counter using 45 nm technology and simulate its transient characteristics  12. Design the schematic of 6T RAM using 45 nm technology and simulate its transient characteristics  13. Design and implementation of Flash Memory with Cadence tool.  14. Design and implementation of Different Analog to Digital converter (ADC) with Cadence tool.  15. Simulate substrate bias (Body) effect in CMOS inverter.	5.			er/full adder using 45 nm	technolo	gy and si	mulate its	
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transient characteristics  Design the schematic of 6T RAM using 45 nm technology and simulate its transient characteristics  Innovative  13. Design and implementation of Flash Memory with Cadence tool.  Design and implementation of Different Analog to Digital converter (ADC) with Cadence tool.  15. Simulate substrate bias (Body) effect in CMOS inverter.	10.	_		egister using 45 nm technol	logy and	simulate it	s transient	
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Innovative         13.       Design and implementation of Flash Memory with Cadence tool.         14.       Design and implementation of Different Analog to Digital converter (ADC) with Cadence tool.         15.       Simulate substrate bias (Body) effect in CMOS inverter.	12.	Design the	schematic of 6T R	AM using 45 nm technolo	ogy and s	imulate its	s transient	
Design and implementation of Different Analog to Digital converter (ADC) with Cadence tool.  15. Simulate substrate bias (Body) effect in CMOS inverter.	Innovative							
Cadence tool.  15. Simulate substrate bias (Body) effect in CMOS inverter.	13.	Design and	l implementation of	Flash Memory with Caden	ce tool.			
	14.	Design and implementation of Different Analog to Digital converter (ADC) with						
Mode of Evaluation Test / Quiz / Assignment / Mid Term Exam / End Term Exam	15.	15. Simulate substrate bias (Body) effect in CMOS inverter.						
	Mode of 1	Evaluation	Test / Quiz	/ Assignment / Mid Term I	Exam / Er	nd Term E	xam	



Department of Electronics and Communication Engineering								
Course:- Master of Technology								
VLSI Design and Systems								
Semester	Second	Subject Title	Advanced ASIC and F Design	PGA	Code	VDM 201		
Course Co	omponents	Credits	Contact Hours	L	T	P		
Program	Core (PC)	03	Contact Hours	3	0	0		
	ination	Theory	Weightage:	CWA	MSE	<b>ESE</b>		
Duratio	on (Hrs)	03	Evaluation	25	25	50		
	P	<u> </u>	nced Digital Integrated	Circuit				
			urse Outcomes					
CO 1		•	Cs, CMOS Logic and ASIC					
CO 2		ding about partition action of ASIC	ning, floor planning, place	ement an	d routing	including		
CO 3	110	the concepts of AS pes of FPGA.	SIC and FPGA in design	ning vari	ous archit	ecture of		
CO 4	manageme		d in ASIC design, includir ication, debug and test, esign.					
CO 5	Evaluation	of SOC based integ	grated circuits for various	FPGA a	pplications	3		
CO 6	Designing	of ASIC family usir	ng Xilinx tool to optimize	the devic	e perform	ance.		
					_			
Unit No.	Content							
Unit 1:	Introduction: Types of ASICs, Design flow, CMOS transistors CMOS design rules, Combinational logic cell, Sequential logic cell, Transistors as resistors, Transistor parasitic capacitance, Logical effort, Library cell design, Library architecture.					10		
Unit 2:	ASIC Physical Design System partition, partitioning, partitioning methods, interconnect delay models and measurement of delay, floor planning, placement, Routing, Circuit extraction, DRC.					9		
Unit 3:	FPGA Architecture: Field Programmable gate arrays, Logic blocks, routing architecture, Design flow technology, Xilinx XC4000, ALTERA's FLEX 8000/10000, ACTEL's ACT-1,2,3 and their speed performance Case studies: Altera MAX 5000 and 7000, Altera MAX 9000, Spartan II and Virtex II FPGAs					10		
Unit 4:	Trade off issues at System Level Optimization with regard to speed, area and power, asynchronous and low power system design. ASIC physical design issues, System Partitioning, Power Dissipation, Partitioning Methods							
Unit 5:	System On Chip Design Design using Xilinx Family, System on Chip Design, SoC Design Flow, Platform based and IP based SoC designs, Basic Concept of Bus – Based					8		



	communication architectures, On- chip communication architectures standards, Low power SoC designs			
Total Hours				

		Textbooks				
1.	M.J.S .Smith, "Appearson Education	<i>oplication - Specific Integrated Circuits</i> ", Addison –Wesley Longman Inc n, 1 <sup>st</sup> Edition, 2008.				
2.	Pasricha and N.Dutt, "On-Chip Communication Architectures System on Chip Interconnect", Elsveir", 1st Edition, 2008, .					
		Reference Books				
3.	M. Rabaey, A. C <i>Perspective</i> ", 2 <sup>nd</sup>	handrakasan, and B.Nikolic, " <i>Digital Integrated Circuit Design</i> Edition, PHI 2003.				
4.						
Mo	de of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.				



Over the state of	www.geu.ac.in							
	Department of Electronics and Communication Engineering							
	Master of Technology							
VLSI Design and Systems								
Semester Second		Subject Title	Digital System Design Verilog HDL	using	Code	VDM 202		
Course Con		Credits	Contact Hours	L	T	P		
Program C		03	Connect Hours	3	0	0		
Examin		Theory	Weightage: Evaluation	CWA	MSE	ESE		
Duration	(Hrs)	03		25	25	50		
			ite: Digital Electronics					
T.			urse Outcomes					
		is course, the stude		7 '1 11	DI 1			
			implementation through V			1		
(02	verification	1	ogic synthesis using Veri	log HDL	and its	impact in		
			and sequential circuits.					
		er defined primitives						
			ent types of digital modelling	_				
		implementation of V st benches.	erilog code of several digit	al circuit	s using Vei	rılog HDL		
ļ								
Unit No.	Content					Hours		
Unit 1:	Modules, Ports, Hierarchical names.  Gate-Level Modeling:				8			
Unit 2:	Gate types, Gate delays.  Dataflow Modelling: Continuous assignments, Delays, Expressions, Operators and Operands. Operator types, Examples.  Behavioural Modelling: Structured procedures, Procedural assignments, Timing controls, Conditional statements, Multiway branching, Loops, Sequential and parallel Blocks, Generate blocks, Examples.			10				
Unit 3:	Task and Functions: Differences between tasks and functions, Tasks, Functions. Useful Modelling Techniques: Procedural continuous assignments. Overriding perameters. Conditional					8		
Switch-Level Modelling: Switch-Modelling elements, examples.  Unit 4: User-Defined Primitives: UDP basics, Combinational UDPs, Sequential UDPs, UDP table shorthand symbols, Guidelines for UDP design.  Unit 5: Writing Test Benches:						8		
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Basic test benches, Test bench structure, Constrained random stimulus generation, Object-oriented programming and Assertion-based verification.	
Total Hours	42

	Textbooks				
1.	Samir Palnitkar, "Verilog HDL", Pearson Education, 2nd Edition, 2003.				
2.	Mark Zwolinski, "Digital System Design with System Verilog", Pearson Education, 1st Edition,				
	2009.				
	Reference Books				
3.	J. Bhasker, "Verilog HDL Synthesis-A practical Prime", Star galaxy Press,1st Edition, 1998				
4.	J. Bhasker, "Verilog HDL Primer", Pearson Education", 3rd Edition, 2015				
5.	Peter J. Ashenden, "Digital Design: An Embedded Systems Approach Using VERILOG",				
	Elsevier, 1st Edition, 2008.				

Mode of Evaluation	Test / Ouiz / Assignment / Mid Term Exam / End Term Exam.
Wide of Lithaution	rest / Quiz / restignment / who rem Exam / End rem Exam:



	Department of Electronics and Communication Engineering							
	Master of Technology							
	VLSI Design and Systems							
Semester	Second	Subject Title	Advanced VLSI Circuit	Testing	Code	VDM 203		
Course Co	omponents	Credits	Contact Hours	L	T	P		
Program	Core (PC)	03	Contact Hours	3	0	0		
	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE		
Duratio	on (Hrs)	03		25	25	50		
			site: VLSI Technology					
**	T (1 0 (1		urse Outcomes					
•	•	is course, the stude						
CO 1			nodeling and fault simulati		•			
CO 2		· ·	or combinational and sequ			1.11.		
CO 3	Apply the observabili	2	level testability Measures	, SCOAF	controlla	bility and		
CO 4		ıy. fferent memory testi:	ng algorithms					
CO 5		evaluate scan archit						
CO 6		ing algorithms for V						
000	Design test	ing digorithms for v	Est components.					
Unit No.	Content					Hours		
	Introduction:							
Unit 1:	Role of testing, Digital and analog VLSI testing, VLSI technology trends affecting testing.  VLSI Testing Process and Test Equipment: Types of testing, Automatic test equipment, Multi-Site testing, Electrical parametric testing.  Test Economics and Product Quality: Defining costs, Production benefit-cost analysis, Economics of testable design, The rule of ten, Yield, Test data analysis.  Fault Modelling: Defects, Errors and Faults, Functional versus Structural testing, A glossary of fault models, Single stuck-at fault, Logic and Fault Simulation: Simulation for design verification, Simulation for test evaluation				10			
Unit 2: Unit 3:	a global problem, Definitions, Test generation systems, Test compaction, Significant combinational ATPG algorithms and sequential circuit test generation.  Memory Test:  Memory density and defect trends. Faults. Memory test levels. March test					8		
Unit 4:	Fundamental Techniques for Logic Testing							



Unit 5:	Embedded Core Test Fundamentals: Introduction to embedded core testing, Core, Core-based design, Reuse core deliverables, Core DFT issues, Development of reusable core, Scan testing the isolated core, Scan testing the non-core logic, User defined logic chiplevel DFT concerns, Memory testing with BIST.		
Total Hours			

	Textbooks					
1.	Viswani D. Agarval Michael L. Bushnell, "Essentials of electronic testing for digital memory					
	& mixed signal VLSI circuit", Kluwer Academic Publications, 1st Edition ,1999.					
2.	Alfred L. Crouch, "Design for test for digital IC's and embedded core systems", PHI, 1st Edition.1999.					
	Reference Books					
3.	Parag. K. Lala, " <i>Digital circuit testing and testability</i> ", Academic Press, 1st Edition, 1997.					
4.	Ashok K. Sharma, "Semiconductor memories technology, testing and reliability", Prentice-					
	Hall of India Private Limited, New Delhi, 1st Edition, 1997.					

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



Department of Electronics and Communication Engineering							
	Master of Technology						
<u> </u>	VLSI Design and Systems  Substituting the Design of VDM						
Semester Second		Subject Title	Low Power VLSI De	sign	Code	204	
	omponents	Credits	Contact Hours	L	T	P	
	ım Core	03	Commen 110m/s	3	0	0	
	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE	
Duration	on (Hrs)	03	0 0	25	25	50	
	1	<b>Pre-requisite:</b> Adva	nced Digital Integrated (	Circuit			
			urse Outcomes				
	<u> </u>	is course, the stude					
CO 1	_		ledge of low power VLSI	design,			
CO 2		static and dynamic	· · · · · · · · · · · · · · · · · · ·				
CO 3	T .		uits and advanced low pow			es.	
CO 4			quired to minimize the lear		er.		
CO 5			v power analog and digital	circuits.			
CO 6	<b>Design</b> of 1	ow power memory of	levices.				
Unit No.	Content					Hours	
Unit 1:	Introduction to Low Power VLSI: Overview, Need for Low Power VLSI Digital Integrated Circuits, Basic Principles of Low Power Design, Physics of Power Dissipation; Technology and Device Effect on Low Power: Transistor Sizing, Gate Oxide Thickness, Impact of Technology Scaling, Technology & Device innovation.				10		
Unit 2:	Sources of Power Dissipation in MOS Devices:  Power Estimation Dynamic Power Dissipation: Short Circuit Power			8			
Unit 3:	Logic Circuits and Advanced Techniques: Logic circuits, Special Techniques: Architecture and Systems; Emerging				8		
Unit 4:	Leakage Power Minimization Approaches: Synthesis in Low Power Design, Test of Low Voltages CMOS Circuits;				8		
Unit 5:	Low Power Techniques: Low Power Static RAM Architectures, Low Power SRAM/DRAM Design, Low Energy Computing using Energy Recovery Techniques, Software Design for Low Power, CAD Tools for Low Power Synthesis.					8	
Total Hours							

Textbooks/ Reference Books:						
1.	Gary Yeap, "Practical Low Power Digital VLSI Design", Springer, 1st Edition, 1998.					



- 2. Kaushik Roy and Sharat Prasad, "Low Power CMOS VLSI Circuit Design", 1st Edition, 2000.
- 3. J. B. Kuo and J. H. Lou, Low "Voltage CMOS VLSI Circuits", Wiley, 1st Edition, 1999.
- **4.** J. M. Rabaey, A. P. Chandrakasan and B. Nikolic, "*Digital Integrated Circuits: A Design Perspective*", 2<sup>nd</sup>edition, Pearson, 2003.

<b>Mode of Evaluation</b>	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



	Depa	rtment of Electroni	cs and Communication E	ngineerin	ıg	
	•	·	er of Technology			
		VLSI I	Design and Systems			
Semester Second		Subject Title	Verilog HDL Lab		Code	VDM 251
Course Components		Credits	Contact Hours	L	T	P
Program Core (PC)		02		0	0	4
Examination		Practical	Weightage: Evaluation	CWA	MSE	ESE
Duratio	on (Hrs)	03	Weightage. Evaluation	25	25	50
		Pre-requis	site:Digital Electronics			
			urse Outcomes			
		is course, the stude				
CO 1			gning through Verilog HD			
CO 2			s using Verilog HDL in FP			
CO 3	<b>Analyse</b> various combinational and sequential circuits using Verilog HDL simulation codes.					
CO 4	Design vari	ous digital systems	using Verilog HDL simula	tion code	es.	
Exp. No.	Name of th	e Experiment				
1.	Design and simulation of XOR gate using NAND gate only.					
2.	Design and simulation of comparator.					
3.	Design and	simulation of Full A	Adder and Full Subtractor.			
4.			plexer and Demultiplexer.			
5.		simulation of Encod				
6.			ip-Flops and D Flip-flop.			
<i>7</i> .	Design and simulation of JK Flip-Flops and T Flip-flop.					
8.	Design and simulation of UP-DOWN counter/Decade counter.					
9.	Design and simulation of different registers.					
10.	Design and simulation of bidirectional and universal shift register					
11.	Design and simulation of binary multiplier.					
12.	FPGA Implementation of basics logic gates.					
13.	Design and simulation of Finite State Machine (FSM) using "Function" in Verilog.					
14.	Design and simulation of Finite State Machine (FSM) without using "Function" in Verilog.					
Innovative						
15.		ementation of Flip-1	flops.			
16.	FPGA Implementation of binary multiplier.					
17.	Design and simulation of floating-point divider.					
18.	As suggested by faculty and lab in-charge.					

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



Department of Electronics and Communication Engineering							
Master of Technology							
		VLSI I	Design and Systems				
Semester Second		Subject Title	VLSI Physical Design Lab		Code	VDM 252	
Course Components		Credits	Contact House	L	T	P	
Program Core (PC)		02	Contact Hours	0	0	4	
Examination		Practical	Weightage: Evaluation	CWA	MSE	ESE	
Duratio	on (Hrs)	03	Weightage. Livatation	25	25	50	
	Pre-r	<b>equisite:</b> Digital Ele	ectronics, Digital VLSI Circ	cuit Desig	gn		
		Со	urse Outcomes				
		is course, the stude					
CO 1			t, tools, and basic scripting	ζ.			
CO 2			design for VLSI chip.				
CO 3	Analyse placement, routing, and power Planning for different circuits.						
CO 4	Design circ	uits using Verilog H	IDL, waveform Debugging	, and syn	thesis.		
Exp. No.	Name of th	e Experiment					
1.	Familiarization with Linux environment, and basic scripting using Verilog HDL.						
2.	Design, simulation, and test of an 8-bit counter with instructions using Verilog HDL.						
3.	Synthesis of 8-bit counter circuit with instructions using Verilog HDL.						
4.	Placement and power planning of 8-bit counter circuit in cadence digital implementation tool of 8-bit counter circuit.						
5.	Routing of 8-bit counter circuit in cadence digital implementation tool in gpdk 90 technology.						
6.	Design, simulation, and test of a Half adder with instructions using Verilog HDL.						
7.	Synthesis o	f Half adder circuit	with instructions using Ver	ilog HDI			
8.	Placement and power planning of Half adder circuit in Cadence digital implementation tool of Half adder circuit.						
9.	Routing of Half adder circuit in Cadence digital implementation tool in gpdk 90 technology.						
10.	Design, simulation, and test of a Full adder with instructions using Verilog HDL.						
11.	Design, simulation, and test of a Half subtractor with instructions using Verilog HDL.						
12.	Synthesis of Half subtractor circuit with instructions using Verilog HDL.						
Innovative	Innovative						
13.	Design, simulation, and test of a Full subtractor with instructions using Verilog HDL.						
14.	Routing of Full subtractor Circuit in Cadence Digital Implementation tool in gpdk 90 technology.						
15.	Design, simulation, and Test of a Full subtractor with instructions using Verilog HDL.				og HDL.		

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



	Department of Electronics and Communication Engineering						
Master of Technology							
		VLSIL	Design and Systems		1	VDM	
Semester Third		Subject Title	Modelling and Simulati		Code	351	
Course Co		Credits	Contact Hours	L	T	P	
Program (	`	02	Contact Hours	0	0	4	
Exami		Practical	Weightage: Evaluation	CWA	MSE	ESE	
Duratio	, ,	03		25	25	50	
	Pre-reg		Devices and Circuits, Digit	al Electro	onics		
			urse Outcomes				
		is course, the stude					
CO 1			actor devices and circuit us				
CO 2	•		various digital and analog			0.11	
CO 3			CAD and Xilinx tools for	the imple	ementation	of digital	
CO 4	and analog		manfammanaa yaina MATI	AD and	VTCAD		
CO 4	Evaluate v	arious MOS devices	performance using MATI	LAB and	VICAD.		
Exp. No.	Name of th	ne Experiment					
1.			nplementation of Multista	re Amnli	fier		
2.						er)	
	Study of Cadence tool for the implementation of analog circuits (CS Amplifier).  Implementation of a novel circuit and its performance analysis using Cadence tool (Flip-						
3.	•	g pass transistors).	it and its performance and	y 515 u 5111g	3 Cadence	tool (1 lip-	
,			CMOS (NMOS/PMOS)	using	VTCAD	and their	
4.	Design and simulation of CMOS (NMOS/PMOS) using VTCAD and their characteristics analysis.						
5.	Design and simulation of Dual Gate MOSFET using VTCAD and their characteristics analysis.						
6.	Design and simulation of Gate All Around FET (GAA-FET) using VTCAD and their characteristics analysis.						
7.			sing VTCAD and their ch	aracterist	ics analysi	S.	
8.			sis of RC coupled amplifie				
9.	To plot the drain characteristics for n-channel MOSFET using MATLAB for						
<i>,</i>	implementation of MOSFET models in linear and saturation region.						
1.0	To plot the transfer characteristics for n-channel MOSFET in linear region and extract						
10.	the various parameters (like threshold voltage $(V_{th})$ , Transconductance $(g_m)$ , Mobility						
	(μ) and on-off current ratio (I <sub>on</sub> /I <sub>off</sub> ) using MATLAB.						
11.	To plot the transfer characteristics for n-channel MOSFET in saturation region and						
11,	extract the various parameters (like threshold voltage $(V_{th})$ , Transconductance $(g_m)$ , Mobility( $\mu$ ) and on-off current ratio $(I_{on}/I_{off})$ using MATLAB.						
			ng condition using Xilinx.				
12	Government wants to give subsidy to the citizens, so they decided that if income is						
12.	greater than subsidy then income itself is the final income. Otherwise, subsidy will be						
added to income to get the total income.							
Innovative							
13.	FPGA implementation of various logic gates in Xilinx tool.						
14.	Design and Simulation of universal gates in VTCAD tool.						
<i>15.</i>	Design and Simulation of Tri-Gate in VTCAD tool.						



**Mode of Evaluation** 

Test / Quiz / Assignment / Mid Term Exam / End Term Exam



Department of Electronics and Communication Engineering  Master of Technology  VLSI Design and Systems								
VLSI Design and Systems								
Semester First Subject Title Advanced Nanotechnology Code	VDM 191							
Course Components Credits L T	P							
Program Elective (PE)(I) 03 Contact Hours 3 0	0							
Examination Theory Weightage: Evaluation CWA MSE	ESE							
<b>Duration (Hrs)</b>   03   25   25	50							
Pre-requisite: Basics of Physics and Chemistry								
Course Outcomes								
Upon completion of this course, the students will be able to	2 . 1							
<b>Remember</b> the concepts of emerging world of nanoscience, Knowledge of electron devices and carbon based nanoelectronics devices.	f single-							
CO 2 Understand the various top-down and bottom-up approaches for nano synthesis.	material							
CO 3 Apply the acquired knowledge to develop novel nanomaterials.								
Analyse the properties of nanomaterials using various scanning probe techniques spectroscopic techniques for material characterization.	ques and							
CO 5 Evaluate the performance of nanotechnology related devices for various in applications.	ndustrial							
CO 6 Utilise analytical tools in nanoscale engineering.								
Unit No.   Content   1	Hours							
Unit 1: Introduction to Nanotechnology: Overview, Historical background, Importance of nanoscale, Bottom-up approaches, Top-down approaches, Functional approaches.	3							
Unit 2:  Nano Materials:  Fundamental concepts of nanomaterials, Allotropes of carbon, Graphene, Graphene nanoribbons, Fullerenes, Fullerites, Carbon nanotubes (CNTs), Bucky paper.								
Nano Electronics: Approaches to Nano electronics, Fabrication of integrated circuits, Introduction to microelectromechanical systems (MEMS), Nanoelectromechanical systems (NEMS), Nanowires, Nano-Circuits, Quantum wire, Quantum well.								
it 4:  Nano-Engineering Devices and Nano- Medicine:  Lab on chip, Micromachinery, Nanomotor, Nanopore, Nano sensor,  Quantum point contact, Synthetic molecular motors, Medical applications of nanomaterials.								
Quantum point contact, Synthetic molecular motors, Medical applications of nanomaterials.								
Quantum point contact, Synthetic molecular motors, Medical applications of nanomaterials.  Analytical Tools in Nanoscale Engineering and Nanolithography:  Atomic force microscopy (AFM). Scanning tunnelling microscope (STM)	10							

## Textbooks



1.	Shunri Oda, David Ferry, "Nanoscale Silicon Devices", CRC Press, Taylor & Francis Group,					
	1 <sup>st</sup> Edition, 2016					
2.	Robert Puers, "Nanoelectronics: Materials, Devices, Applications", Wiley, 1st Edition 2017.					
	Reference Books					
3.	Suprio Datta, "Lessons from nanoelectronics", World Scientific publisher, 1st Edition, 2012.					
4.	Gabriel M. Rebeiz, " <i>RF MEMS: Theory, Design, and Technology</i> ", Wiley, 1st Edition, 2003.					
5.	Julian W. Gardner, "Microsensors, MEMS and Smart Devices", Wiley, 1st Edition, 2002.					

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



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Department of Electronics and Communication Engineering						
			er of Technology			
		VLSI 1	Design and Systems			
Semester	Ontimization Techniques in					
Course Co	omponents	Credits		L	T	P
	Elective (I)	03	Contact Hours	3	0	0
Exam	ination	Theory	Weightness Euglantion	CWA	MSE	ESE
Duratio	on (Hrs)	03	Weightage: Evaluation	25	25	50
		Pre-requisite: V	LSI Technology and Design	gn		
		Со	urse Outcomes			
Upon com	pletion of th	nis course, the stude	ents will be able to			
CO 1	Recall the parameters	•	delling techniques based	on inco	orporating	empirical
CO 2	Understan techniques.	_	e parameters and yield	estimatio	on of op	timization
CO 3	Apply the	knowledge of conve	x optimization techniques.			
CO 4	Analyse ar	nd <b>understand</b> Gene	tic algorithm in VLSI desi	gn.		
CO 5	Assess and	evaluate FPGA for	automatic test generation.			
CO 6	Implemen	t optimization techni	ques in VLSI design.			
Unit No.	Content					Hours
Unit 1:	Unit 1:  Statistical Modelling:  Modelling sources of variations, Monte Carlo techniques, Process variation modelling- Pelgrom's model, Principal component-based modelling, Quad tree based modelling, Performance modelling-response Surface methodology, Delay modelling, Interconnect delay models.				ng, Quad	8
Unit 2:	Statistical Performance, Power and Yield Analysis: Statistical timing analysis, Parameter space techniques, Bayesian networks				8	
Unit 3:	Convex Optimization: Convex sets, Convex functions, Geometric programming, Trade-off and sensitivity analysis, Generalized geometric programming, Geometric programming applied to digital circuit gate sizing, Floor planning, Wire sizing, Approximation and fitting- monomial fitting, Maxmonomial fitting, Posynomial fitting.				9	
Genetic Algorithm:  Introduction, GA Technology-Steady state algorithm-Fitnessscaling-Inversion GA for VLSI design, Layout and test automation- Partitioning-automatic placement, Routing technology, Mapping for FPGA- Automatic test generation- Partitioning algorithm taxonomy-multiway partitioning Hybrid Genetic-Encoding-Local Improvement-WDFR comparison of casstandard cell placement-GASP algorithm-unified algorithm.					9	
Unit 5:	GA Routing Procedures and Power Estimation:					8



ı	estimation-application of GA-standard cell placement-GA for ATG-problem					
	encoding- fitness function-GA Vs conventional algorithm.					
	Hardware/Software Co-Designs.					
	Total Hours					

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	Textbooks				
1.	Ashish Srivastava, Dennis Sylvester, David Blaauwi, "Statistical Analysis and Optimization				
	Ashish Srivastava, Dennis Sylvester, David Blaauwi, "Statistical Analysis and Optimization for VLSI: Timing and Power", Springer, 1st Edition, 2005.				
2.	Kalyanmoy Dev, "Optimization for Engineering Design: Algorithms and Examples", PHI				
	Learning, 2 <sup>nd</sup> Edition, 2001.				
	Reference Books				
3.	PinakiMazumder, E. Mrudnick, "Genetic Algorithm for VLSI Design, Layout and test Automation", Prentice Hall, 1st Edition, 2002.				
	Automation". Prentice Hall, 1st Edition, 2002.				

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.

	Depo	artment of Electron	ics and Communication E	ngineerin	ıg			
		Mas	ter of Technology					
	VLSI Design and Systems							
Semester	First	Subject Title	Theory and Application Embedded System		Code	VDM 193		
Course Co	omponents	Credits		L	T	P		
_	Elective (I)	03	Contact Hours	3	0	0		
Exam	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE		
Duratio	on (Hrs)	03	Weightage. Evaluation	25	25	50		
	1	<b>Pre-requisite:</b> Micro	ocontrollers & Embedded S	ystems				
		Ce	ourse Outcomes					
Upon com	pletion of th	nis course, the stud	ents will be able to					
CO 1	Recall the	basic concept of em	bedded system.					
CO 2	Understan	d the architecture a	nd instruction sets of PIC m	nicroconti	rollers.			
CO 3		knowledge of system	· ·					
CO 4	Analyse st	ructure of RTOS ba	sed embedded systems.					
CO 5	Evaluate A	ARM-32 bit process	ors as the advanced series n	nicrocont	roller.			
CO 6	Integrate t	the concepts of adva	nced embedded systems for	r develop	ing project	īs.		
Unit No.	Content					Hours		
Unit 1:	Embedded Systems: Embedded vs General computing system, classification, application and				8			
Unit 2:	PIC Architectures:			8				
Unit 3:	System Firmware Design: Hardware Software Co-Design embedded firmware design approaches			8				
	RTOS Based Embedded System Design:				8			
Unit 4:				eduling.				
Unit 4: Unit 5:	and Thread  ARM-32 b  Thumb-2 to  M3, Various	ls, Multiprocessing a bit Microcontroller echnology and appli	and Multitasking, Task Sch : cations of ARM, Architectunitecture, General Purpose	re of AR		8		



	Textbooks				
1.	Raj Kamal, " <i>Microcontrollers: Architecture, Programming, Interfacing and System Design</i> ", Pearson Education India, 2 <sup>nd</sup> Edition, 2005.				
2.	J. Morton, "The PIC Microcontroller", Newnes, 3rd Edition, 2005.				
	Reference Books				
3.	A. Sloss, D. Symes, C. Wright, "Arm System Developer's Guide: Designing and optimizing system software", Morgan Kauffman Publisher, Illustrated edition, 2004.				
4.	K. V. Shibhu, "Introduction to Embedded Systems", Tata McGraw Hill, 1st Edition, 2009.				
5.	Frank Vahid, Tony Givargis, " <i>Embedded System Design, A Unified Hardware, Software Approach</i> ", Wiley Publications, 3 <sup>rd</sup> Edition, 1999.				

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



Course Components   Credits   Contact Hours   Code   Institute   Contact Hours   Code   Institute   Contact Hours   Code   Institute   Institute   Code   Institute   Institute		T.		. 10					
Semester									
Semester   First   Subject Title   Digital Signal Processing for VLSI									
Course Components									
Program Elective (PE) (I)  Examination Theory Duration (Hrs)  Duration (Hrs)  O3  Pre-requisite: Digital Signal Processing  Course Outcomes  Upon completion of this course, the students will be able to  CO I Recall the basic concepts of DFT- FFT in FIR filters and IIR filters.  CO 2  Understand iteration bound, pipelining and parallel processing.  CO 3  Apply the knowledge of retiming and parallel processing by using various convolution techniques.  CO 4  Analyse algorithmic strength reduction in filters transforms and pipelined and par recursive filters.  CO 5  Evaluate scaling and round off noise computation processes.  CO 6  Design and develop high-speed VLSI based devices.  Unit No.  Unit 1:  Introduction:  Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG-DFG.  Iteration Bound:  Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate data-flow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming:  Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution.  Cook-Toom algorithm, Winograd algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms:  Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filters order filters.  Pipelined and Parallel Recursive Filters:  Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	Semester	First	•		•		VDM 194		
CPE (I)	Course Co	mponents	Credits		L	T	P		
Duration (Hrs)   03   Weightage: Evaluation   25   25   50			03	Contact Hours	3	0	0		
Pre-requisite: Digital Signal Processing  Course Outcomes  Upon completion of this course, the students will be able to  CO 1 Recall the basic concepts of DFT- FFT in FIR filters and IIR filters.  CO 2 Understand iteration bound, pipelining and parallel processing.  Apply the knowledge of retiming and parallel processing by using various convolution techniques.  CO 4 Analyse algorithmic strength reduction in filters transforms and pipelined and par recursive filters.  CO 5 Evaluate scaling and round off noise computation processes.  CO 6 Design and develop high-speed VLSI based devices.  Unit No. Content  Introduction:  Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG-DFG.  Iteration Bound:  Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate dataflow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming:  Definitions-properties and problems- Solving systems of inequalities, Retiming techniques Fast Convolution:  Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms:  Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filters:  Pipelined and Parallel Recursive Filters:  Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	Exami	nation	Theory	Wajahtaan Englustion	CWA	MSE	ESE		
Upon completion of this course, the students will be able to  CO 1 Recall the basic concepts of DFT- FFT in FIR filters and IIR filters.  CO 2 Understand iteration bound, pipelining and parallel processing.  CO 3 Apply the knowledge of retiming and parallel processing by using various convolution techniques.  CO 4 Analyse algorithmic strength reduction in filters transforms and pipelined and par recursive filters.  CO 5 Evaluate scaling and round off noise computation processes.  CO 6 Design and develop high-speed VLSI based devices.  Unit No. Content Hou Introduction:  Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG-DFG.  Iteration Bound:  Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate dataflow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming:  Definitions-properties and problems- Solving systems of inequalities, Retiming techniques Fast Convolution:  Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms:  Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filters.  Pipelined and Parallel Recursive Filters:  Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	Duratio	n (Hrs)	03	weighlage: Evaluation	25	25	50		
Upon completion of this course, the students will be able to  CO 1 Recall the basic concepts of DFT- FFT in FIR filters and IIR filters.  CO 2 Understand iteration bound, pipelining and parallel processing.  Apply the knowledge of retiming and parallel processing by using various convolution techniques.  CO 4 Analyse algorithmic strength reduction in filters transforms and pipelined and par recursive filters.  CO 5 Evaluate scaling and round off noise computation processes.  CO 6 Design and develop high-speed VLSI based devices.  Unit No. Content Hou Introduction:  Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG-DFG.  Iteration Bound:  Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate dataflow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming:  Definitions-properties and problems- Solving systems of inequalities, Retiming techniques  Fast Convolution:  Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms:  Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters.  Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filters cosine transform and Inverse DCT, Parallel architectures for rank order filters.  Pipelined and Parallel Recursive Filters:  Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital			Pre-requisite:	Digital Signal Processing					
CO 1   Recall the basic concepts of DFT- FFT in FIR filters and IIR filters.   CO 2   Understand iteration bound, pipelining and parallel processing.   CO 3   Apply the knowledge of retiming and parallel processing by using various convolution techniques.   CO 4   Analyse algorithmic strength reduction in filters transforms and pipelined and paraceursive filters.   CO 5   Evaluate scaling and round off noise computation processes.   CO 6   Design and develop high-speed VLSI based devices.   Unit No.   Content   Hou Introduction:			Со	urse Outcomes					
CO 2 Understand iteration bound, pipelining and parallel processing.  CO 3 Apply the knowledge of retiming and parallel processing by using various convolution techniques.  CO 4 Analyse algorithmic strength reduction in filters transforms and pipelined and parallel grecursive filters.  CO 5 Evaluate scaling and round off noise computation processes.  CO 6 Design and develop high-speed VLSI based devices.  Unit No. Content Hou Introduction:  Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG-DFG.  Iteration Bound:  Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate dataflow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming:  Definitions-properties and problems- Solving systems of inequalities, Retiming techniques  Fast Convolution:  Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms:  Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filters:  Pipelined and Parallel Recursive Filters:  Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	Upon com	pletion of th	nis course, the stude	ents will be able to					
CO 3	CO 1	Recall the	basic concepts of DI	FT- FFT in FIR filters and	IIR filters	S.			
CO 3	CO 2	Understan	d iteration bound, pi	ipelining and parallel proce	essing.				
recursive filters.  CO 5	CO 3	Apply the	knowledge of reti			using va	rious fast		
Unit No.   Content   Hou	CO 4			eduction in filters transfor	ms and p	ipelined ar	nd parallel		
Unit No.   Content   Hou	CO 5								
Unit 1:  Introduction: Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG-DFG.  Iteration Bound: Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate data-flow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming: Definitions-properties and problems- Solving systems of inequalities, Retiming techniques Fast Convolution: Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms: Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filters: Pipelined and Parallel Recursive Filters: Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	CO 6								
Unit 1:  Introduction: Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG-DFG.  Iteration Bound: Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate data-flow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming: Definitions-properties and problems- Solving systems of inequalities, Retiming techniques Fast Convolution: Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms: Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filters: Pipelined and Parallel Recursive Filters: Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital		8							
Unit 1:  Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG-DFG.  Iteration Bound:  Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate data-flow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming:  Definitions-properties and problems- Solving systems of inequalities, Retiming techniques  Fast Convolution:  Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms:  Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filters.  Pipelined and Parallel Recursive Filters:  Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	Unit No.	Content					Hours		
Unit 2:  Iteration Bound: Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate data- flow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.  Retiming: Definitions-properties and problems- Solving systems of inequalities, Retiming techniques Fast Convolution: Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms: Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filters: Pipelined and Parallel Recursive Filters: Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	Unit 1:	Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP					8		
Unit 3:  Definitions-properties and problems- Solving systems of inequalities, Retiming techniques Fast Convolution: Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic convolution, Design of fast convolution algorithm by inspection.  Algorithmic Strength Reduction in Filters and Transforms: Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filters.  Pipelined and Parallel Recursive Filters: Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	Unit 2:	Iteration Bound: Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate data- flow graph. Pipelining and parallel processing: Pipelining of FIR digital				8			
Algorithmic Strength Reduction in Filters and Transforms: Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filter.  Pipelined and Parallel Recursive Filters: Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital	Unit 3:	Retiming: Definitions-properties and problems- Solving systems of inequalities, Retiming techniques Fast Convolution: Cook-Toom algorithm, Winograd algorithm, Iterated convolution, Cyclic				8			
clustered look ahead-parallel processing for IIR filters and problems.  Unit 5: Scaling and Round off Noise:  9	Algorithmic Strength Reduction in Filters and Transforms:  Parallel FIR filters discrete cosine transform and Inverse DCT, Parallel architectures for rank order filters-odd even merge sort architecture, Rank order filter architecture, Parallel rank order filters-running order merge order sorter, Low power rank order filter.  Pipelined and Parallel Recursive Filters:  Pipeline interleaving in digital filters- Pipelining in 1st order IIR digital filters- Pipelining in higher-order IIR filters-clustered look ahead and stable clustered look ahead-parallel processing for IIR filters and problems.								



	Scaling and round off noise- State variable description of digital filters, Scaling and round off noise computation, Round off noise in pipelined IIR filters, Computation using state variable description, Slow-Down, Retiming and pipelining.			
Total Hours				

Textbooks					
1.	K. K. Parhi, "VLSI Digital Signal Processing", John-Wiley, 1st Edition, 1999.				
2.	John G. Proakis, Dimitris G. Manolakis, " <i>Digital Signal Processing</i> ", Prentice Hall of India. 3 <sup>rd</sup> Edition, 1996.				
Reference Books					
3.	Richard J. Higgins, " <i>Digital signal processing in VLSI</i> ", Prentice Hall, 1st Edition, 1990.				

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



	Department of Electronics and Communication Engineering						
	Master of Technology						
<b>Semester</b> First		VLSI I Subject Title	Design and Systems  Robust Control System Code		Code	VDM 195	
Course Co	omponents	Credits		L	T	P	
	Elective		Contact Hours				
_	(I)	03		3	0	0	
	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE	
Duratio	on (Hrs)	03	" cightage. L'ununon	25	25	50	
			isite: Control Systems				
			urse Outcomes				
		nis course, the stude					
CO 1	<del></del>	e motivation of robu					
CO 2	Compute performance		and performance along	with ro	obust stał	oility and	
CO 3	_	bustness and uncerta					
CO 4		bust stability and loc					
CO 5	Acquire th	e fundamentals of H	2 and H∞ control				
CO 6	Design fee	dback control systen	ns				
Unit No.	Content Hours						
Unit 1:	Introduction and Background: Control System representations, System stabilities, Coprime factorisation and stabilising controllers, signals and 04				04		
Unit 2:	systems norms.  Modeling of uncertain systems: Introduction to concepts of model uncertainty, including both parametric and dynamic uncertainty, Linear fractional transformations and canonical forms.						
Unit 3:	Robustness Problems: Linear fractional transformations and canonical forms. Performance measured via (induced) norms. Robust stability and performance problems. Solution of SISO robustness problems.						
Unit 4:	Computer-Aided Analysis Techniques: Introduction to the structured singular value for robustness analysis of MIMO systems. Conversion of robustness problems to canonical M- $\Delta$ form. The small gain theorem and approximate computation of $\mu$ via efficient upper and lower bounds. Computer-aided tools for $\mu$ -analysis based on the Matlab Robust Control Toolbox.						
Unit 5:	Synthesis and Controller: Design Optimal controller design including H <sub>2</sub> and H <sub>infinity</sub> optimal control. Scaled H <sub>infinity</sub> -optimal control problems and μ-synthesis. Computer-aided tools to implement D,G-K iteration for advanced controller design. Lower order controllers: Absolute error approximation methods, reduction via fractional factors, relative error approximation methods, and frequency weighted approximation methods, Design case studies.						
		Total	Hours			36	

Textbooks	
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1.	U. Mackenroth, "Robust Control Systems-Theory and Case Studies", Springer International				
	Edition, Springer, 2010				
2.	Kemin Zhou, "Essentials of Robust Control", Prentice-Hall, 1st Edition, 1998				
3.	Gu, Da-Wei, Petkov, Petko, Konstantinov, Mihail M, "Robust Control Design with				
	MATLAB", Springer International Edition, Springer, 2009				
	Reference Books				
4.	Richard.C.Dorf and R.T Bishop, "Modern Control System", P.H.I				
5.	S P Bhattacharya, L H Keel, H Chapellat, "Robust Control: The Parametric Approach",				
	Prentice-Hall, 1995				
6.	P C Chandrasekharan, "Robust Control of Linear Dynamical Systems", Academic Press,				
	1996.				

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



Department of Electronics and Communication Engineering						
	Master of Technology					
	VLSI Design and Systems					
Semester First		Subject Title	Control of Advanced Electric Machine		Code	VDM 196
Course Co		Credits		L	T	P
Program (PE)		03	Contact Hours	3	0	0
Exami		Theory	Weightage: Evaluation	CWA	MSE	ESE
Duratio	n (Hrs)	03	Weightuge. Lyminmion	25	25	50
			Basic Electrical Engineerin	g		
			urse Outcomes			
		is course, the stude				
CO 1			peration and power convert			
CO 2	Synchrono	us reluctance motor	f operation and power of			
CO 3	Understan brushless E	· •	nciple of operation, theo	ory of to	rque prod	luction in
CO 4	Explain the	e control aspect of sp	pecial electrical machines			
CO 5	Demonstrate an understanding of the fundamental control practices associated with				iated with	
CO 6	Summariz	e the various perform	nance characteristics of spe	ecial elec	trical macl	nines
Unit No.	Content					Hours
Unit 1:	Stepper Motors - Constructional features, principle of operation, modes of excitation, single phase stepping motors, torque production in variable Reluctance (VR) stepping motor, Dynamic characteristics, Drive systems and circuit for open loop control, Closed loop control of stepping motor, control of stepper motor using microcontroller.			10		
Unit 2:	Switched Reluctance Motors - Constructional features, principle of operation. Torque equation, Power controllers, Characteristics and control. Microprocessor based controller. Sensor less control.			8		
Unit 3:	Synchronous Reluctance Motors-Constructional features: axial and radial air gap Motors. Operating principle, reluctance torque – 8 Phasor diagram, motor characteristics.				8	
Unit 4:	Permanent Magnet Brushless DC Motors - Commutation in DC motors, Difference between mechanical and electronic commutators, Hall sensors, Optical sensors, Multiphase Brushless motor, Square wave permanent magnet brushless motor drives, Torque and EMF equation, Torque-speed characteristics, Controllers-Microprocessor based controller. Sensorless control.  10  Total Hours  36			10		
,						

Textbooks and Reference Books								
1.	Kenjo T., Sugawara A, "Stepping Motors and their Microprocessor Contro	,",						
	Clarendon Press, Oxford, 1st Edition, 1994	•						



- **2.** Miller T. J. E., "*Switched Reluctance Motor and Their Control*", Clarendon Press, Oxford, 1<sup>st</sup> Edition, 1993.
- 3. Miller T. J. E., *Brushless Permanent Magnet and Reluctance Motor Drives*, Clarendon Press, Oxford, 2<sup>nd</sup> Edition, 1989.
- 4. B K Bose, *Modern Power Electronics & AC drives*, Pearson, 1<sup>st</sup> Edition, 2002.

<b>Mode of Evaluation</b>	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



	www.geu.ac.in						
Department of Electronics and Communication Engineering							
Master of Technology  VLSI Design and Systems							
Semester Second		Subject Title	Micro-Sensors and M	d MEMS C		VDM 291	
Course Co	omponents	Credits		L	T	P	
Program	Elective (II)	03	Contact Hours	3	0	0	
	ination	Theory	Waiahtaan Englantian	CWA	MSE	ESE	
Duratio	on (Hrs)	03	Weightage: Evaluation	25	25	50	
		Pre-requis	site: VLSI Technology				
		Co	urse Outcomes				
_	pletion of th	is course, the stude	ents will be able to				
CO 1			ifferent sensors and actuato				
CO 2			iaturization of a sensor and			ce a micro	
			ts integration with microele				
CO 3	Apply varied MEMS.	ous fabrication techr	nologies for miniaturization	n of senso	ors and act	tuators for	
CO 4			s of sensors and actuators.				
CO 5		ne behaviour of MEN					
CO 6	Create app life applicate	-	gning of different MEMS b	ased devi	ices for var	rious real-	
Unit No.	Content Hours						
	Microfabrication and Micromachining: Integrated circuit processes, Bulk micromachining, Isotropic etching and anisotropic etching, Wafer bonding, High aspect-ratio processes (LIGA).						
Unit 1:	Integrated	circuit processes, B	ulk micromachining, Isot			10	
Unit 1: Unit 2:	Integrated anisotropic Physical M Classificati Sensor pri	circuit processes, B etching, Wafer bond licro-Sensors: on of physical sens	ulk micromachining, Isot ding, High aspect-ratio pro- sors, Integrated, Intelligen- bles: Thermal sensors, E	cesses (L	IGA).	8	
	Integrated anisotropic  Physical M Classificati Sensor pri Mechanical  Micro actu Electromag actuators, M	circuit processes, B etching, Wafer bond licro-Sensors: on of physical sensoriciples and examples sensors, Chemical antors: metic and thermal material actuator examples actuator examples actuator systems, Successive etching.	ulk micromachining, Isot ding, High aspect-ratio pro- sors, Integrated, Intelligen- bles: Thermal sensors, E	nt, Smart Electrical	sensors, sensors, of micro romotors		
Unit 2:	Integrated anisotropic  Physical M Classificati Sensor pri Mechanical  Micro actu Electromag actuators, M Micro actua TV projecto  Surface M One or requiremen materials, S	circuit processes, B etching, Wafer bond licro-Sensors: on of physical sensor nciples and examples and examples and examples are not considered at the material and thermal material actions actuator examples are systems, Successor. icromachining: two sacrificial lates, Polysilicon surficial surficial distribution dioxide, Silicon dioxide, Silicon dioxide, Silicon dioxide, Silicon systems: Successor.	sors, Integrated, Intelligent bles: Thermal sensors, Eand biosensors.	at, Smart Electrical design mps, Mic ads, Micromother commeterials	sensors, sensors, sensors, of micro romotors ro-Mirror machining ompatible, Surface	8	
Unit 2: Unit 3:	Integrated anisotropic Physical M Classificati Sensor pri Mechanical Micro actu Electromag actuators, M Micro actua TV projecto Surface M One or requiremen materials, S micromach mechanism Application All-mechan sensors, RF E.G. DNA	circuit processes, B etching, Wafer bond licro-Sensors: on of physical sensor nciples and examples and examples and examples are not a lators: metic and thermal material actuator examples actu	sors, Integrated, Intelligences, Integrated, Intelligences, Internal sensors, Enand biosensors.  Inicro-actuation, Mechanica bles, Microvalves, Micropures stories, Ink-Jet printer he processes, Surface reface micromachining, Con nitride, Piezoelectric in	at, Smart Electrical al design mps, Microm Other comaterials ors, Geatic actuals, Medicalons: Need	sensors, sensors, sensors, of micro romotors ro-Mirror machining ompatible, Surface ar trains tors and I devices d for RF	8	



	Textbooks					
1.	Chang Liu, "Foundations of MEMS", Pearson, 2 <sup>nd</sup> Edition, 2012.					
2.	Rai - Choudhury P., "MEMS and MOEMS Technology and Applications", PHI Learning					
	Private Limited, 1st Edition, 2009.					
3.	Julian W. Gardner, "Microsensors, MEMS and Smart Devices", Wiley, 1st Edition, 2002.					
Reference Books						
4.	Gabriel M. Rebeiz, " <i>RF MEMS: Theory, Design, and Technology</i> ", Wiley, 1st Edition, 2003.					
5.	Stephen D. Senturia, " <i>Microsystem design</i> ", Springer, 1st Edition, 2006.					

<b>Mode of Evaluation</b>	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



	D	unter and of Elastrania	on and Communication E			
	Бера		cs and Communication E er of Technology	ngineerir	ıg	
			Design and Systems			
Semester	Second	Subject Title	RF Microelectronics D	evices	Code	VDM 292
Course Co	omponents	Credits		L	T	P
Program	Elective ) (II)	03	Contact Hours	3	0	0
	ination	Theory	W-:-1-4 F14:	CWA	MSE	ESE
Duratio	on (Hrs)	03	Weightage: Evaluation	25 25		50
	Pre-requis	<b>ite:</b> Electronics Dev	ices and Circuits, Microwa	ave Engir	neering,	
		Co.	urse Outcomes			
Upon com	pletion of th	is course, the stude				
CO 1			technology in RF design:			
CO 2			chniques for RF circuits.			
CO 2			and transistor modelling	, Mobile	RF comm	nunication
CO 3	systems and	d basics of multiple a	access techniques.			
CO 4	Analyse the	e concept of BJT and	d MOSFET behaviour at R	F frequer	ncies.	
CO 5	Assess and	evaluate Radio frequ	uency devices.			
CO 6	CO 6 Design and develop RF based microelectronic devices.					
Unit No.   Content					Hours	
Unit 1:	Introduction: Introduction to RF and wireless technology: Complexity, Design and applications, Choice of technology. Basic concepts in RF design, Nonlinearly and time variance, Random processes and noise.					8
Unit 2:	Modulation Techniques for RF Circuits:  Definition of sensitivity, Dynamic range, Conversion gains and distortion				10	
Unit 3:	Detectors and Transistor Modelling:  Mobile RF communication systems and basics of multiple access techniques.  Pageiver and transmitter architectures and testing beterodyne. Homodyne					8
Unit 4:	warious technologies, Design of mixers at GHz frequency range. Various mixers, Their working and implementations, Oscillators: Basic topologies VCO and definition of phase noise. Noise-power trade-off. Resonator less VCO design. Quadrature and single-sideband generators.					8
Unit 5:	RF Synthesizer: Radio frequency synthesizes: PLLS, Various RF synthesizer architectures and frequency dividers, Power amplifiers design. Linearization techniques,					8



	Design issues in integrated RF filters. Some discussion on available CAD tools for RF VLSI designs.			
Total Hours				

	Textbooks				
1.	B. Razavi, " <i>RF Microelectronics</i> ", Prentice-Hall PTR, 2 <sup>nd</sup> Edition, 2012.				
2.	T. H. Lee, "The Design of CMOS Radio-Frequency Integrated Circuits", Cambridge				
	University Press, 1 <sup>st</sup> Edition, 1998.				
	Reference Books				
3.	R. Jacob Baker, H. W. Li, and D.E. Boyce, "CMOS circuit design, Layout and simulation",				
	Prentice-Hall of India, 1st Edition, 1998.				

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.
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	Dana	ertment of Fleetvon	ics and Communication E	ทสเทอองเน	ıa	
	Дери		ter of Technology	ngineerin	<u>'8</u>	
			Design and Systems			
Semester	Semester Second Subject Title VLSI Circuits for Biomedical Application Code		Code	VDM 293		
Course C	omponents	Credits		L	T	P
	Elective () (II)	03	Contact Hours	3	0	0
Exam	ination	Theory	Wajahtaan Englustion	CWA	MSE	ESE
Duratio	on (Hrs)	03	Weightage: Evaluation	25	25	50
	Pre-requisite	e: Advanced VLSI (	Circuit Design, CMOS Ana	log Circu	it Design	
		Со	urse Outcomes			
Upon com	pletion of th	is course, the stude	ents will be able to			
CO 1	Recall the	concepts of neuroch	emical and neuro potential	devices.		
CO 2			nvolved in the design of C	MOS circ	cuits for in	nplantable
	÷		s biomedical applications.			
CO 3			reless medical application.			
CO 4			nterfacing with neural syst		.•	
CO 5		he process of neur ding, and neurostim	o-signal acquisition and a ulation.	amplifica	tion, neur	ochemical
CO 6	Develop Cl	MOS circuits for bio	omedical applications.			
Unit No.   Content						Hours
Unit 1:	Introduction: Wireless integrated neurochemical and neuropotential circuits: Introduction, Neurochemical sensing, Neuropotential sensing, RF telemetry and power harvesting in implanted devices, Multimodal electrical and chemical sensing. Visual cortical neuroprosthesis: A system approach: Introduction, System architecture, Prosthesis exterior body unit and wireless link, Body				9	
Unit 2:	implantable unit, System prototype.  CMOS Circuits for Biomedical Implantable Devices: Introduction, Inductive link to deliver power to implants, High data rate transmission through inductive links, Energy and bandwidth issues in multichannel bio-potential recording. Towards self—powered sensors and circuits for biomedical implants: Introduction, Stress, Strain and fatigue predication, In vivo strain measurement and motivation. Fundamental of piezoelectrictransduction and power delivery, Sub-microwatt piezo-powered VLSI circuits.				9	
Unit 3:	CMOS Circuits for Wireless Medical Application: Introduction, Spectrum regulations for medical use, Integrated receiver and transmitter architecture, Radio architecture, System budget, Low noise amplifier, Mixer, Polyphase filter, Power amplifier, PLL. Error correcting codes for in vivo RF wireless links.			8		
Unit 4: Microneedles: Introduction, Fabrication methods for hollow out –of –plane microneedles, Application for microneedles. Integrated circuit for neural interfacing: Introduction, nature of neural signals, Neural signal amplification.						
Unit 4: Unit 5:	Application Introduction	n, Fabrication methor for microneedles	. Integrated circuit for n ignals, Neural signal ampli	eural int		8



Integrated circuit for neural interfacing (Neurochemical recording), Integrated circuit for neural interfacing (Neural Stimulation): Introduction, Electrode configuration and tissue volume conductor, Electrode- Electrolyte Interface, Efficacy, Stimulus generator, Stimulation front end circuits.	
Total Hours	42

	Textbooks				
1.	Kris Iniewski, " <i>VLSI Circuit Design for Biomedical Application</i> ", Artech House Publishers, 1 <sup>st</sup> Edition, 2008.				
2.	D. A. Hodges, H. G. Jackson and R. A. Saleh, "Analysis and Design of Digital Integrated Circuits in Deep Submicron Technology", Tata McGraw-Hill, 3 <sup>rd</sup> Edition, 2003.				
	Reference Books				
3.	Parag. K. Lala, "Digital circuit testing and testability", Academic Press, 1st Edition, 1997.				
4.	Ashok K. Sharma, "Semiconductor memories technology, testing and reliability", Prentice-				
	Hall of India Private Limited, 1 <sup>st</sup> Edition, 2002.				

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



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Department of Electronics and Communication Engineering						
Master of Technology						
	1	VLSI L	Design and Systems			
	G 1		Microwave & MM-w			VDM
Semester	Second	Subject Title Integrated Circuits a	ind	Code	294	
Course C	2	Ca a dita	Applications	7	T	P
	omponents	Credits	Contact Hours		T	<u> </u>
_	Elective (II)	03	Contact Hours	3	0	0
	ination	Theory		CWA	MSE	ESE
1	on (Hrs)	03	Weightage: Evaluation	25	25	50
Dirimi	(1115)		: Microwave Engineering	23	23	
			urse Outcomes			
Unon com	nletion of th	is course, the stude				
			MMIC and MM-wave tec	chnologie	es and the	ir various
CO 1	application	•				
CO 2			cesses Circuit of Microwa	ve Integra	ated MIC.	
			and passive circuit eleme			and MM-
CO 3	wave techn	ology.				
CO 4	Analyse the various measurement systems using MM-wave technology.					
CO 5	Evaluate th	ne microwave compo	onents for designing micro	wave Inte	grated circ	cuits.
CO 6	<b>Design</b> of N	MMIC using MM-W	ave Technology.			
Unit No.	Content					Hours
Unit 1:	technologies and materials, Encapsulation and mounting of active devices, Introduction to MM-wave integrated circuits, GaAs fabrication technology			nges and thin film devices, chnology	10	
Unit 2:	and various processes, Materials used for MM-wave integrated guides.  Passive components: Introduction, Inductors, Capacitors, Resistors, Via-holes, and grounding, Microstrip components, Coplanar circuits, Multilayer techniques, Micromachined passive components.				8	
Unit 3:	Active Semiconductor circuit elements:  Active device technologies and design approaches, Fabrication and modeling: Bipolar junction transistor, Hetero junction bipolar transistor, High electron mobility transistor, MESFET, CMOS, BiCMOS.					10
Unit 4:	Measurement Techniques: Introduction, Test fixture measurements, Probe station measurements, Thermal and cryogenic measurements, Experimental field probing techniques, MM-wave measurement techniques: Electric field probe, Measurement of attenuation constant and guide wavelength. Measurement at radiation loss at bents.					8
	System Application: MICs in phased array radars, MICs in satellite television systems, Microwave radio systems, Monolithic MM-wave transceiver.					



## Total Hours 42

	Textbooks				
1.	I. D. Robertson and S. Lucyszyn, " <i>RFIC and MMIC design and technology</i> ", The Institute of Electrical Engineers, 2 <sup>nd</sup> Edition 2001.				
2.	Leo G. Maloratsk, " <i>Passive RF and Microwave Integrated Circuits</i> ", Elsevier, 1 <sup>st</sup> Edition, 2004.				
3.	K. C. Gupta and A. Singh, " <i>Microwave Integrated circuit</i> ", John Wiley & Sons, 2 <sup>nd</sup> Edition, 1974				
4.	E. Carey and S. Lidholm, "Millimeter wave Integrated Circuit", Springer, 2 <sup>nd</sup> Edition, 2005				
	Reference Books				
5.	I. Kneppo, J. Fabian, P. Bezousek, P. Hrnicko and M. Pavel, " <i>Microwave Integrated Circuits</i> ", 1 <sup>st</sup> Edition, Springer.				
6.	S. K. Koul, "Millimeter Wave and Optical Dielectric Integrated Guides and Circuits", John Wiley & Sons, 1st Edition, 1997.				
7.	Duixian Liu, Ulrich Pfeiffer, Janusz Grzyb and Brian Gaucher, "Advanced Millimeter-wave Technologies: Antennas, Packaging and Circuits", Wiley, 1st Edition, 2009.				

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



Demonstructure of Electronics and Communication Engineering							
	Department of Electronics and Communication Engineering						
Master of Technology  VLSI Design and Systems							
Semester	Renewable Energy Resources		Code	VDM 295			
Course C	omponents	Credits		L	T	P	
. ~	Elective (II)	03	Contact Hours	3	0	0	
	ination on (Hrs)	Theory 03	Weightage: Evaluation	<i>CWA</i> 25	<b>MSE</b> 25	<b>ESE</b> 50	
		Pre-requ	uisite: Basic Physics				
			urse Outcomes				
_	î	is course, the stude					
CO 1			ar Power Generation and so				
CO 2	Illustrate t systems.	he photovoltaic cha	racteristics, classifications	, fuel ce	lls and wi	nd energy	
CO 3	Demonstra	te the Geothermal e	nergy for conversion in ele	ectrical er	nergy.		
CO 4	Analyse the	e performance analy	sis of Fuel cell and MHD.				
CO 5	Evaluate th	ne various renewable	e power generation techniq	ues and c	ompare th	e results.	
CO 6	<b>Develop</b> so	lar panels, fuel cells	and wind energy techniqu	es.			
Unit No.	Content					Hours	
Unit 1: Solar Thermal Energy: Solar radiation flat plant collectors and their materials, application and performance, focusing of collectors and their materials, applications and performance solar thermal power plants, thermal energy storage for solar heating and cooling, limitations.			and their	08			
Unit 2:  Photo voltaic System-Solar cell characteristics, solar cell classifications, solar cell module, panel and Array constructions, Maximizing solar PV output and Load Matching, Maximum Power Point Tracking (MPPT), Balance of system components, Solar PV applications			solar PV	08			
Unit 3:	<b>Fuel Cells:</b> Principle of working of various types of fuel cells and their working performance and limitations				06		
Unit 4:	Wind Energy: Wind power and its sources, site selection, criterion,			06			
Unit 5:  Geothermal Energy: Resources of geothermal energy, thermodynamics of geo-thermal energy conversion-electrical conversion, non-electrical conversion, environmental considerations.  Magneto-hydrodynamics (M H D): Principle of working of M H D Power plant, performance and limitations.  Bio-mass: Availability of bio-mass and its convention theory.				08			
		Total	Hours			36	

## **Textbooks**



1.	B.H Khan, "Non-Conventional Energy Resources" Tata McGraw-Hill Education 2nd Edition					
2.	Max Kurtz, "Handbook of Engineering Economics: Guide for Engineers, Technicians,					
	Scientists, and Managers", McGraw-Hill, 1st Edition, 1984					
3.	A. Mani, " <i>Handbook of solar radiation Data for India</i> ." Allied Publishers Pvt. Ltd., 1 <sup>st</sup> Edition, 1980.					
	Edition, 1980.					
4.	Peter Auer, "Advances in Energy System and Technology", Vol. I & II Edited by					
	Academic Press, 1st Edition,					
5.	F.R. the MITTRE, "Wind Machines" by Energy Resources and Environmental Series".					
	Van Nostrand Reinhold Inc., U.S.; 2nd Revised Edition, 1980					
	Reference Books					
6.	Frank Kreith, "Solar Energy Hand Book",					
7.	N. Chermisinogg and Thomes, C. Reign, "Principles and Application of solar Energy".					
	TMH, 2 <sup>nd</sup> Edition, 1980.					

Mode of Evaluation Test / Quiz / Assignment / Mid Term Exam / End Term Exam.	
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Department of Electronics and Communication Engineering										
	Master of Technology									
	VLSI Design and Systems									
Semester         Second         Subject Title         Multivariable Control Systems         Code		Code	VDM 296							
Course C	omponents	Credits		L	T	P				
. ~	Elective (II)	03	Contact Hours	3	0	0				
Exam	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE				
Duratio	on (Hrs)	03	weightage: Evaluation	25	25	50				
		Pre-requisite: I	Basic Electrical Engineerin	g						
			urse Outcomes							
		is course, the stude								
CO 1			control in multivariable s							
CO 2	Extend the	e basic knowledge	and understanding of the	e multiva	ariable sy	stems				
CO 3		nt the multivariable and study of their be	le systems through oper ehaviour.	and cl	osed loop	transfer				
CO 4	Analyze a	multivariable dyna	amic system							
CO 5			mance and robustness of	f a closed	d-loop sy:	stem				
CO 6	Design an	appropriate contro	oller for the multivariable	system						
				2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2						
Ilaid NIa	Content   Hours									
Unit No.	Content					Hours				
Unit 1:	Introduct in the m Elements	ultivariable case,	ble systems: - Classical Introduction to multiv theory, Limitations on	ariable	control,	Hours 6				
	Introduct in the mi Elements SISO and Analysis o state space	ultivariable case, of linear systems MIMO systems. of Multi-Variable of Multi-variable tra	Introduction to multiv	variable perform namic an riable po	control, nance in alysis in le – zero					
Unit 1:	Introduct in the man Elements SISO and Introduct Analysis of state space concept, of analysis.  Multi – Si analysis an RGA, loop pure integri	ultivariable case, of linear systems MIMO systems.  of Multi-Variable of Multi-variable trajuantitative measured loop designs and loop pairing, the pairing of nonlineator modes, loop p	Introduction to multive theory, Limitations on System:-Open loop dynamsfer function, Multi var	variable perform namic an riable pod loop of on of into op pairing for syst	control, nance in alysis in le – zero dynamic reraction ng using em with	6				
Unit 1: Unit 2:	Introduct in the many Elements SISO and Introduct state space concept, or analysis.  Multi – Sianalysis and RGA, loop pure integrate controller, Introduct steady state	ultivariable case, of linear systems MIMO systems.  of Multi-Variable of Multi-Variable of Multi-variable transmittative measurements and loop pairing, the pairing of nonlineator modes, loop prontroller tuning from to De-couplers.	Introduction to multive theory, Limitations on System:-Open loop dynamsfer function, Multi varies of singularity, closed:-Preliminary consideration relative gain array, loop ear system, loop pairing pairing for non-square systems.	variable perform amic an riable pod loop of into op pairing for systems, mutang, feasing, fea	alysis in le – zero dynamic eraction ng using em with ulti-loop	8				
Unit 1:  Unit 2:  Unit 3:	Introduct in the man Elements SISO and Introduct state space concept, or analysis.  Multi – Si analysis and RGA, loop pure integrate controller, Introduct steady state value decorposign of	ultivariable case, of linear systems MIMO systems.  of Multi-Variable e, Multi-variable traquantitative measured loop designs: and loop pairing, the pairing of nonlineator modes, loop prontroller tuning from to De-couplers te de-coupler designs; and multivariable systems.  f multivariable systems	Introduction to multive theory, Limitations on System:-Open loop dynamsfer function, Multi varies of singularity, close relative gain array, locar system, loop pairing for non-square system multi-loop system.	variable perform amic an riable pod loop of into op pairing for systems, mutang, feasiling by	alysis in le – zero dynamic reraction ng using em with ulti-loop libility of singular Design	8				

	Textbooks
1.	Y. S. Apte, <i>Linear multivariable control system</i> , Tata McGraw Hill, 1 <sup>st</sup> Edition, 1981



2.	Dale E. Seborg, Thomas F. Edgar, and Duncan A. Mellichamp, <i>Process Dynamics and Control</i> , Wiley India, 1 <sup>st</sup> Edition, 2003.						
	Reference Books						
3.	3. C. T. Chen, <i>Linear system theory and design</i> , Oxford University Press, 1999.						
4.	4. John Bay, Fundamentals of linear state space systems, Tata McGraw Hill, 1998.						
5.	Wilson Rugh, <i>Linear system theory</i> , Prentice Hall, 1996.						

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



	www.geu.ac.in							
Department of Electronics and Communication Engineering								
Master of Technology								
VLSI Design and Systems								
Semester	Third	Subject Title	Organic Electronics Devices and Circuits Code		Code	VDM 391		
Course Co	omponents	Credits		L	T	P		
_	Elective (III)	03	Contact Hours	3	0	0		
Exam	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE		
Duratio	on (Hrs)	03	Weightage. Evaluation	25	25	50		
j	Pre-requisite		Engineering, Electronics D	evices an	d Circuits.	ı		
			urse Outcomes					
Upon com	^	is course, the stude						
CO 1	semicondu	ctor devices.	ncepts and limitations of			con-based		
CO 2			and classification of organ					
CO 3	Apply the electronic of		arge transport in organic n	naterials	for differe	nt organic		
CO 4		-	organic electronic devices	S.				
CO 5		he performance of or						
CO 6	Analyse th	e different properties	s of OLED.					
	r							
Unit No.	Content					Hours		
Unit 1:	Introductio Organic se and Gate e concept of	miconductors: p-typ lectrodes, Gate diele charge transport in o d inorganic semicor	e: Conducting polymers and ee and n-type semiconduct ectrics, Substrate. Energy organic semiconductors; Conductors including the me	ors, Sour band diag mparison	ce, Drain gram and between	9		
Unit 2:	Organic Thin Film Transistors (OTFTs): Introduction; Operating principle; Output and transfer characteristics; Classification of various organic thin film transistors (OTFT) structures; Performance perspectage: Impact of structural perspectage on behaviour of				10			
Unit 3:	Organic Light Emitting Diodes (OLEDs) Introduction; Organic materials for OLEDs; Classification of OLEDs, Operating principle; Output and transfer characteristics; Analysis of OLED performance: Optical, Electrical and thermal properties, Merits and demerits; Stability issues; OLEDs as display applications.							
Unit 4:  Organic Solar Cell: Introduction; Operating principle; Characteristics; Materials for organic solar cells; Classification of organic solar cell- Single layer, Bi-layer and bulk hetero junction organic solar cell; Merits and demerits; Applications and future scope.					7			
Unit 5:	Organic So					8		



Introduction; Working principle and organic sensing materials for pressu	re
sensors (Piezoresistive, Piezoelectric, and Capacitive sensor), Temperatu	re
sensors, Humidity sensors and pH sensor; comparison between organic ar	nd
conventional sensors including merits, demerits and limitation	s;
Applications of organic sensors; Basics of ionic polymer-metal composite	es
(IPMC) and its applications.	
Total Hours	42

	Textbooks						
1.	Hagen Klauk, "Organic Electronics: Materials, Manufacturing and Applications", Wiley-						
	VCH VerlagGmbh& Co. KGaA, Germany, 1st Edition, 2006.						
2.	Klaus Mullen, UllrichScherf, "Organic Light Emitting Devices: Synthesis, Properties and						
	Applications", Wiley-VCH VerlagGmbh& Co. KGaA, Germany, 1st Edition, 2005.						
3.	Johannes Karl Fink, " <i>Polymeric Sensors and Actuators</i> ", John Wiley & Sons, 1st Edition, 2012.						
	Reference Books						
4.	Hagen Klauk, "Organic Electronics II: More Materials and Applications", Wiley-VCH						
	VerlagGmbh& Co. KGaA, Weinheim, Germany, 1st Edition, 2012						
5.	Flora Li, Arokia Nathan, Yiliang Wu, Beng S. Ong, "Organic Thin Film Transistor						
	Integration: A Hybrid Approach", Wiley-VCH, Germany; 1st Edition, 2011.						
6.	Wolfgang Brutting, "Physics of Organic Semiconductors", Wiley-VCH VerlagGmbh& Co.						
	KGaA, Germany, 2 <sup>nd</sup> Edition, 2005.						
7.	Daniel A. Bernards, Róisín M. Owens, George G. Malliaras, "Organic Semiconductors in						
	Sensor Applications". Springer Science & Business Media, 1st Edition, 2008.						

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.
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Department of Electronics and Communication Engineering								
Master of Technology								
	VLSI Design and Systems							
Semester	Semester         Third         Subject Title         Memory Design and Testing         Code		Code	VDM 392				
Course Co	omponents	Credits		L	T	P		
Program Elective (PE) (III)		03	Contact Hours	3	0	0		
	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE		
Duratio	on (Hrs)	03		25	25	50		
		Pre-requisite:	Low Power VLSI Design	1				
			urse Outcomes					
		nis course, the stude						
CO 1			rledge of CMOS memory of	levices.				
CO 2 CO 3			ndamental VLSI chip.					
CO 4			ormance digital VLSI ment equired to implement low p					
CO 5			gital VLSI memory system		mory emp.			
CO 6		low power memory of		3.				
	Design of	low power memory c	de v 1005.					
Unit No.	Content					Hours		
Unit 1:	memory cell: SRAM Cell, DRAM Cell Trends in Non-Volatile Memory Design and Technology, Ferroelectric memory, Basic Operation of Flash				es of mory Flash	10		
Memory Cells, Advances in Flash-Memory Design and Technology.  Basics of RAM Design and Technology: Devices, NMOS Static Circuits, NMOS Dynamic Circuits, CMOS Circuits, Basic Memory Circuits, Scaling Law.  On-Chip Voltage Generators: Substrate-Bias Voltage (VBB) Generator, Voltage Up Converter, Voltage Down-Converter, Half-VDD Generator, Examples of Advanced On-Chip Voltage Generators.				8				
Unit 3:	DRAM Circuits: High-Density Technology, High-Performance Circuits, Catalog Specifications of the Standard DRAM, Basic Configuration and Operation of the DRAM Chip, Chip Configuration, Address Multiplexing, Fundamental Chip, Multi-divided Data Line and Word Line, Read and Relevant Circuits, Write and Relevant Circuits, Refresh-Relevant Circuits, Redundancy Techniques, On-Chip Testing Circuits, High Signal-to-Noise Ratio DRAM Design and Technology, Trends in High S/N Ratio Design, Data-Line Noise Reduction, Noise Sources.					8		
Unit 4:	High-Performance Subsystem Memories: Hierarchical Memory Systems, Memory-Subsystem Technologies, High-					8		



	Subsystem and Chip, Low-Power DRAM Circuits, Low-Power SRAM Circuits.	
Unit 5:	Ultra-Low-Voltage Memory Circuits: Design Issues for Ultra-Low-Voltage RAM Circuits, Reduction of the Subthreshold Current, Stable Memory-Cell Operation, Suppression of, or Compensation for, Design Parameter Variations, Power-Supply Standardization, Ultra-Low Voltage DRAM Circuits, Ultra-Low-Voltage SRAM Circuits, Ultra-Low-Voltage SOI Circuits.	8
	Total Hours	42

	Textbooks
1.	Itoh, K., VLSI Memory Chip Design, Springer, 1st Edition, 2006.
2.	Sharma, A. K., Semiconductor Memories: Technology, Testing and Reliability, Wiley- IEEE
	press, 1 <sup>st</sup> Edition, 2002.
	Reference Books
3.	J. B. Kuo and J. H. Lou, Low "Voltage CMOS VLSI Circuits", Wiley, 1st Edition, 1999.
4.	J. M. Rabaey, A. P. Chandrakasan and B. Nikolic, "Digital Integrated Circuits: A Design
	Perspective", 2 <sup>nd</sup> Edition, Pearson, 2003.

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



Semester   Third   Subject Title   System on Chip Design and Joyatems   Code   VIM 393	Department of Electronics and Communication Engineering							
Course Components   Credits   Contact Hours								
Course Components   Credits   Contact Hours   Contact Hours   Contact Hours			VLSI 1	Design and Systems				
Program Elective (PE) (III)	<b>Semester</b> Third		Subject Title		_			
CPE   (III)	Course Co	mponents	Credits		L	T	P	
Duration (Hrs)   03   Weightage: Evaluation   25   25   50	_		03	Contact Hours	3	0	0	
### Pre-requisite: VLS1 Technology    Course Outcomes	Exami	nation	Theory	Woightago: Evaluation	CWA	MSE	ESE	
Upon completion of this course, the students will be able to  CO 1 Recall the concepts of System-on-Chip (SoC) Testing.  CO 2 Understand the concepts of digital test architectures design.  CO 3 Apply the concepts of SoC on delay testing and low-power testing.  CO 4 Analyse the basics of system/network-on-chip test architectures.  CO 5 Assess and evaluate debug and diagnosis.  CO 6 Implement different testing techniques in SoC.  Unit No. Content Hours  Introduction: Importance of system-on-chip testing, Basics of SoC testing, Basics of memory testing, SoC design examples.  Digital Test Architectures: Scan design, Logic built-In self-test, Test compression, Random-access scan design.  Fault-Tolerant Design: Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes  System/Network-on-Chip Test Architectures: System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies.  SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components. Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid overtesting  Low-Power Testing: Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing.  Coping with Physical Failures, Soft Errors, and Reliability Issues: Signal integrity, Manufacturing defects, Process variations, and Reliability, Soft errors, Defect and error tolerance.	Duratio	n (Hrs)	03	Weightage. Evaluation	25	25	50	
Unit 1:  Content  Unit 1:  System/Network-on-Chip (SoC) testing, Basics of design.  Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes  System/Network-on-Chip (SoC) testing, Design and test practice: Case studies.  System/Network-on-Chip (SoC) testing, Design and test practice: Case studies.  System/Network-on-Chip Test Architectures:  System/Network-on-Chip Test Architectures:  System/Network-on-Chip Test Architectures:  Unit 2:  Unit 3:  Unit 4:  Unit 4:  Unit 5:  Unit 5:  Unit 5:  Unit 6:  Unit 6:  Unit 7:  Unit 7:  Unit 7:  Unit 7:  Unit 8:  Unit 8:  Unit 9:  Unit 1:  Unit 1:  Unit 9:  Unit 9:  Unit 9:  Unit 9:  Unit 1:  Unit 1:  Unit 1:  Unit 1:  Unit 1:  Unit 1:  Unit 3:  Unit 1:  Unit 1:  Unit 3:  Unit 3:  Unit 4:  Unit 9:  Unit 1:  Unit 1:  Unit 3:  Unit 1:  Unit 3:  Unit 1:  Unit 3:  Unit 4:  Unit 2:  Unit 2:  Unit 3:  Unit 3:  Unit 4:  Unit 4:  Unit 4:  Unit 5:  Unit 4:  Unit 5:  Unit 4:  Unit 5:  Unit 5:								
Recall the concepts of System-on-Chip (SoC) Testing.   CO 2								
CO 2 Understand the concepts of digital test architectures design.  CO 3 Apply the concepts of SoC on delay testing and low-power testing.  CO 4 Analyse the basics of system/network-on-chip test architectures.  CO 5 Assess and evaluate debug and diagnosis.  CO 6 Implement different testing techniques in SoC.  Unit No. Content Hours  Introduction: Importance of system-on-chip testing, Basics of SoC testing, Basics of memory testing, SoC design examples. Digital Test Architectures: Scan design, Logic built-In self-test, Test compression, Random-access scan design. Fault-Tolerant Design: Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes  System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies. SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components. Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid overtesting  Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power Built-in self-test, Low-power test data compression, Low-power RAM testing. Coping with Physical Failures, Soft Errors, and Reliability Issues: Signal integrity, Manufacturing defects, Process variations, and Reliability, Soft errors, Defect and error tolerance.	_		•					
CO 3								
CO 4 Analyse the basics of system/network-on-chip test architectures.  CO 5 Assess and evaluate debug and diagnosis.  CO 6 Implement different testing techniques in SoC.  Unit No. Content Hours  Introduction: Importance of system-on-chip testing, Basics of SoC testing, Basics of memory testing, SoC design examples. Digital Test Architectures: Scan design, Logic built-In self-test, Test compression, Random-access scan design. Fault-Tolerant Design: Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes  System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies. SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components. Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid overtesting  Low-Power Testing: Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing.  Coping with Physical Failures, Soft Errors, and Reliability Issues: Signal integrity, Manufacturing defects, Process variations, and Reliability, Soft errors, Defect and error tolerance.					_			
CO 5						•		
Unit No. Content    Introduction:		•	•	•	ctures.			
Unit No. Content  Introduction: Importance of system-on-chip testing, Basics of SoC testing, Basics of memory testing, SoC design examples. Digital Test Architectures: Scan design, Logic built-In self-test, Test compression, Random-access scan design. Fault-Tolerant Design: Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes  System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies. SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components. Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid overtesting  Low-Power Testing: Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing. Coping with Physical Failures, Soft Errors, and Reliability Issues: Signal integrity, Manufacturing defects, Process variations, and Reliability, Soft errors, Defect and error tolerance.				<u> </u>				
Introduction: Importance of system-on-chip testing, Basics of SoC testing, Basics of memory testing, SoC design examples. Digital Test Architectures: Scan design, Logic built-In self-test, Test compression, Random-access scan design. Fault-Tolerant Design: Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes  System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies. SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components. Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid overtesting  Low-Power Testing: Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing. Coping with Physical Failures, Soft Errors, and Reliability, Soft errors, Defect and error tolerance.	CO 6	Implemen	t different testing tec	enniques in SoC.				
Introduction: Importance of system-on-chip testing, Basics of SoC testing, Basics of memory testing, SoC design examples. Digital Test Architectures: Scan design, Logic built-In self-test, Test compression, Random-access scan design. Fault-Tolerant Design: Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes  System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies. SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components. Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid overtesting  Low-Power Testing: Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing. Coping with Physical Failures, Soft Errors, and Reliability, Soft errors, Defect and error tolerance.	Unit No	Contant					Иолия	
Importance of system-on-chip testing, Basics of SoC testing, Basics of memory testing, SoC design examples.  Digital Test Architectures: Scan design, Logic built-In self-test, Test compression, Random-access scan design. Fault-Tolerant Design: Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes  System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies. SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components. Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid overtesting  Low-Power Testing: Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing.  Coping with Physical Failures, Soft Errors, and Reliability Issues: Signal integrity, Manufacturing defects, Process variations, and Reliability, Soft errors, Defect and error tolerance.	Unit No.						Hours	
Unit 2:  System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies. SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components. Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid overtesting  Low-Power Testing: Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing. Coping with Physical Failures, Soft Errors, and Reliability Issues: Signal integrity, Manufacturing defects, Process variations, and Reliability, Soft errors, Defect and error tolerance.	Unit 1:	memory test Digital Test Scan design design. Fault-Tole Fundament	sting, SoC design ex st Architectures: n, Logic built-In self erant Design: tals of fault toleran	amples. Etest, Test compression, Ra	ındom-ac	cess scan	8	
Unit 3:  Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing.  Coping with Physical Failures, Soft Errors, and Reliability Issues: Signal integrity, Manufacturing defects, Process variations, and Reliability, Soft errors, Defect and error tolerance.	Unit 2:	System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies.  SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components.  Delay Testing: Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid over-			8			
I I WIT AT I I I I I I I I I I I I I I I I I	Unit 3: Unit 4:	Low-Power Introduction scan testing Low-power Coping wire Signal integrations,	n, Energy and power g, Low-power built-in r RAM testing. th Physical Failures grity, Manufacturing Defect and error tol	n self-test, Low-power test s, Soft Errors, and Reliab g defects, Process variation terance.	data com	pression,	8	



	Introduction, Yield, components of yield, Photolithography, DFM and DFY, Variability, Metrics for DFX.  Design for Debug and Diagnosis: Introductiontologic design for debug and diagnosis (DFD) structures, Probing technologies, Circuit editing, Physical DFD structures, Diagnosis and debug process.	
Unit 5:	Software-Based Self-Testing: Introduction, Software-based self-testing paradigm, Processor functional fault self-testing, Processor structural fault self-testing, Processor self-diagnosis, testing global interconnect, testing nonprogrammable cores, Instruction-level DFT, DSP-Based Analog/Mixed-signal component testing. Field Programmable Gate Array Testing: Overview of FPGAs, Testing approaches, BIST of programmable resources, Embedded processor-based testing	10
	Total Hours	42

	Textbooks
1.	Laung-Terng Wang, Charles E. Stroud, Nur A. Touba, "System-On-Chip Test Architectures
	Laung-Terng Wang, Charles E. Stroud, Nur A. Touba, "System-On-Chip Test Architectures (Nanometer Design for Testability)", Elsevier, 1 <sup>st</sup> Edition, 2008.
	Reference Books
2.	Erik Larsson, "Introduction to Advanced system- on- chip test design and optimization",
	Springer, 5 <sup>th</sup> Edition, 2006.

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



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	Дера	· ·	ics and Communication E	ngıneerin	ıg	
			ter of Technology Design and Systems			
		V LSI I	VLSI Physical Desi	αn		VDM
Semester Third		Subject Title	Automation	gn	Code	394
Course Co	omponents	Credits		L	T	P
Program (PE)		03	Contact Hours	3	0	0
Exami	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE
Duratio	on (Hrs)	03	Weightage. Evaluation	25	25	50
		Pre-requisite:	Digital VLSI Circuit Desig	n		
		Ca	ourse Outcomes			
Upon com	pletion of th	nis course, the stud	ents will be able to			
CO 1		<b>.</b>	esign automation tools.			
CO 2			ompaction, placement, and	routing a	lgorithms.	
CO 3			ynthesis in VLSI design.			
CO 4		oor planning and rou				
CO 5			g algorithms, allocation, an			
CO 6	Optimize of	design layouts for flo	oor-planning, placement, ar	nd routing	5.	
Unit No.	Content			Hours		
Unit 1:		gn Automation To	ols:			
	logic desig	n, Transistor level	Algorithms and system desidesign, Layout design, Ver			10
Unit 2:	logic design man Layout Co Design rul methods,	n, Transistor level on nagement tools.  Impaction, Placement es, Symbolic layou Algorithms for ion, Wire length es	design, Layout design, Ver	etion, For	mulation Circuit	8
	logic design Design man Layout Co Design rul methods, representat algorithms.  Floor Plan Floor plans	n, Transistor level on agement tools.  Impaction, Placement es, Symbolic layou Algorithms for ion, Wire length estaining and Routing:	ent and Routing: t, Applications of compact constrained graph co	etion, For npaction, thms, Par	mulation Circuit rtitioning	
Unit 2:	logic design Design man Layout Co Design rul methods, representat algorithms. Floor Plan Floor plan routing, Ar Simulation Gate level combination	n, Transistor level on agement tools.  Impaction, Placement tools.  Impaction, Placement tools.  Impaction, Placement tools.  Algorithms for the initial tools and the second tools.  Ining and Routing:  Ining concepts, Shape the arouting, Channel to and Logic Synthem and switch level	ent and Routing: t, Applications of compact constrained graph contimation, Placement algorithmetic and Floor plant routing, Global routing and sis: modelling and simulationsis, ROBDD principles,	etion, For npaction, thms, Par ning, Sizin d its algor	methods, mulation Circuit rtitioning ng, Local rithms.	8
Unit 2: Unit 3:	logic design man Design man Layout Co Design rul methods, representat algorithms.  Floor Plant Floor plant routing, Ar Simulation Gate level combination Construction High-Level Hardware algorithms.	n, Transistor level on agement tools.  Impaction, Placement tools.  Impaction, Placement tools.  Impaction, Placement tools.  Algorithms for ion, Wire length esterning and Routing:  Ining and Routing:  Ining concepts, Shapped a routing, Channel and Logic Synthem and switch level in all logic synthesis in and manipulation of Synthesis:  Impaction in the synthesis is in the synthesis:  Impaction in the synthesis is in the synthesis:  Impaction in the synthesis is in the synthesis:  Impaction in the synthesis in the synthesis is in the synthesis i	ent and Routing: t, Applications of compact constrained graph contimation, Placement algorithmetic and Floor plant routing, Global routing and sis: modelling and simulationsis, ROBDD principles,	etion, For npaction, thms, Par ning, Sizin d its algor Introdu Implem	mulation Circuit retitioning  ng, Local rithms.  action to nentation,	8

	Textbooks
1.	S. H. Gerez, "Algorithms for VLSI Design Automation", John Wiley, 3 <sup>rd</sup> Edition, 2000.
2.	N. A. Sherwani, "Algorithms for VLSI Physical Design Automation", Kluwer, 3 <sup>rd</sup> edition, 1999.



## Reference Books

- 3. M. Sait, H. Youssef, "VLSI Physical Design Automation", World scientific, 1st Edition, 1999.
- 4. M. Sarrafzadeh, "Introduction to VLSI Physical Design", McGraw Hill (IE), student Edition, 1996.

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Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



	Dan	autment of Flactuan	ios and Communication F	nginaavit	10		
	Department of Electronics and Communication Engineering  Master of Technology						
			Design and Systems				
Semester	Third	Subject Title	Power Quality Assess	ment	Code	VDM 395	
Course Co	omponents	Credits		L	T	P	
_	Elective (III)	03	Contact Hours	3	0	0	
Exam	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE	
Duratio	on (Hrs)	03		25	25	50	
			Basic Electrical Engineerin	g			
			urse Outcomes				
Upon com		nis course, the stude					
CO 1	Describe to compensati		of ac transmission system	n, shunt	and series	s reactive	
CO 2	Understan assessment		ortion and processing te	chniques,	and the	eir power	
CO 3	<b>Demonstra</b> characteris	•	principles of FACTS d	evices a	nd their	operating	
CO 4	Analyse St	atic synchronous Co	ompensator (STATCOM).				
CO 5	Estimate t	he working principle	es of devices to improve po	wer qual	ty.		
CO 6	Propose th	e power quality mor	nitoring system and their ha	armonic a	nalysis.		
Unit No.	Content					Hours	
Unit 1:	classification THD-TIF-loccurrence	ality-voltage quality on of power quality i DIN-message wei of power quality	y-overview of power quality measurables. Flicker factor-transic problems-power acceptable ommended practices.	res and so	tandards- nomena-	8	
Unit 2:	Power Assessment under Waveform Distortion & Processing Techniques: Introduction, single phase definitions, three phase definitions, illustrative			8			
Unit 3:	Unit 3:  Power Quality Monitoring: Introduction, transducers, CT, PT, power quality instrumentation, Harmonic monitoring, event recording, flicker monitoring, assessment of voltage and current unbalance, examples of application			6			
Unit 4:	Evaluation of power system harmonic distortion: Introduction, direct harmonic analysis, incorporation of harmonic voltage sources, derivation of network harmonic impedances, solution by direct injection, Representation of individual power system components, implementation of harmonic analysis, post processing and display of results.		6				
Unit 5:	Harmonic Passive fil	Mitigation & Groutering, Harmonic re		n Analys	is-Active	8	



	APFC and Control Techniques, Grounding and wiring—introduction-NEC grounding requirements-reasons for grounding-typical grounding and wiring problems-solutions to grounding and wiring problems.	
Ī	Total Hours	36

	Textbooks and Reference Books
1.	Math H. Bollen , "Understanding Power Quality Problems", Wiley-IEEE Press; 1st Edition,
	1999.
2.	G. T. Heydt Stars " <i>Electric Power Quality</i> ", Circle Publishers, 2 <sup>nd</sup> Edition, 1994.
3.	J. Arrillaga, "Power System Quality Assessment". John Wiley, 2 <sup>nd</sup> Edition, 2000.
4.	Surya Santoso, H. Wayne Beaty, Roger C. Dugan, Mark F. McGranaghan, "Electrical Power
	System Quality", McGraw Hills, 2 <sup>nd</sup> Edition, 2002.

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.



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	Dep	•	ics and Communication E	ngineerii	ıg	
			ter of Technology			
		VLSI I	Design and Systems		1	VDM
Semester		Subject Title	Optimal & Adaptive C	ontrol	Code	396
	omponents	Credits		L	T	P
Program Elective (PE) (III)		03	Contact Hours	3	0	0
	ination	Theory	Weightage: Evaluation	CWA	MSE	ESE
Duratio	on (Hrs)	03	0 0	25	25	50
			Basic Electrical Engineerin	g		
W.T.	1.44 6.41		urse Outcomes			
	î –	nis course, the stude		1 4 1	1.1	
CO 1			nd to define various optima			:
CO 2			linear regulator problem us imality and to solve cont			
CO 3	problem	•	•		inie inieai	regulator
CO 4	Examine minimum time and minimum control effort problems					
CO 5	<b>Evaluate</b> adaptive control problem and to learn the mathematical description of model reference adaptive systems					
CO 6	Design ada	ptive systems using	various techniques			
Unit No.	Content					Hours
Unit 1:	<ul> <li>Problem Formulation: Mathematical model, Physical constraints, Characteristics of the plants, Performance Measure, optimal control problems, selection of performance measure, state regulator problem, output regulator problem.</li> <li>Calculus of Variations: Fundamental concepts, minimization of functions, minimization of Functionals, Lagrange multiplier approach, constrained extrema, Variational approach to optimal control problems, formulation of variational calculus using Hamiltonian Method.</li> </ul>			08		
Unit 2:	Dynamic principle of of dynami equation, a solution us	<b>Programming</b> : Opto f causality, principle c programming — and its application, ing dynamic program	timal control law, Principof invariant imbedding, and computational procedure, one dimensional regulator mming computational procedure.	recurrenc Hamiltor r problen edure.	e relation on-Jacobi n and its	06
Unit 3:	Optimization Problems & Techniques: Pontryagin's minimum principle, control & state variable inequality constraints, A nonlinear Reactor model problem and its solution, Minimum time problems, Minimization of functions, minimization of Functionals, two point boundary value problems.					
Unit 4:	Introduction:-Adaptive Control (Identifier based & Non Identifier based), Applications, Linear feedback, effects of process disturbances, robustness, adaptive schemes and various adaptive control strategies, Parametric models, Parameter identification(One Parameter Case & two Parameter Case).					
Unit 5:	MRAS: M Theory, Re	IT Rule, Lyapunov elation between MR	e System (MRAS) & G Theory, Design of MRAS AS and STR, Non-Linear ack Linearization, Back-s	S using I System: 1	Lyapunov Feedback	07



Back-stepping with tuning functions, Design of Gain-Controllers	Scheduling		
Total Hours			

	Textbooks and Reference Books					
1.	Donald E. Kirk, " <i>Optimal Control Theory: An Introduction</i> ", Prentice-Hall networks series, 10 <sup>th</sup> Edition, 1970.					
2.	Anderson .B. D. O, Moore .J. B, " <i>Optimal control linear Quadratic methods</i> ", Prentice Hall of India, 1 <sup>th</sup> Edition, New Delhi, 1991.					
3.	Sage A. P, White .C. C, "Optimum Systems Control", 2 <sup>nd</sup> Edition, Prentice Hall, 1977.					
4.	Athans M and P L Falb, "Optimal Control-An Introduction to the Theory and its Applications", McGraw Hill Inc, New York, 1th Edition, 1966.					
5.	Sage A P, " <i>Optimum Systems Control</i> ", Prentice –Hall Inc Englewood Cliffs, New Jersey, 2 <sup>nd</sup> Edition, 1968					

Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam.